# Notice for TAIYO YUDEN products

Please read this notice before using the TAIYO YUDEN products.

# **I** REMINDERS

Product information in this catalog is as of October 2016. All of the contents specified herein are subject to change without notice due to technical improvements, etc. Therefore, please check for the latest information carefully before practical application or use of our products.

Please note that TAIYO YUDEN shall not be in any way responsible for any damages and defects in products or equipment incorporating our products, which are caused under the conditions other than those specified in this catalog or individual specification.

Please contact TAIYO YUDEN for further details of product specifications as the individual specification is available.

- Please conduct validation and verification of our products in actual condition of mounting and operating environment before using our products.
- The products listed in this catalog are intended for use in general electronic equipment (e.g., AV equipment, OA equipment, home electric appliances, office equipment, information and communication equipment including, without limitation, mobile phone, and PC). Please be sure to contact TAIYO YUDEN for further information before using the products for any equipment which may directly cause loss of human life or bodily injury (e.g., transportation equipment including, without limitation, automotive powertrain control system, train control system, and ship control system, traffic signal equipment, disaster prevention equipment, medical equipment, highly public information network equipment including, without limitation, telephone exchange, and base station).

Please do not incorporate our products into any equipment requiring high levels of safety and/or reliability (e.g., aerospace equipment, aviation equipment, nuclear control equipment, undersea equipment, military equipment).

When our products are used even for high safety and/or reliability-required devices or circuits of general electronic equipment, it is strongly recommended to perform a thorough safety evaluation prior to use of our products and to install a protection circuit as necessary.

Please note that unless you obtain prior written consent of TAIYO YUDEN, TAIYO YUDEN shall not be in any way responsible for any damages incurred by you or third parties arising from use of the products listed in this catalog for any equipment requiring inquiry to TAIYO YUDEN or prohibited for use by TAIYO YUDEN as described above.

- Please note that TAIYO YUDEN shall have no responsibility for any controversies or disputes that may occur in connection with a third party's intellectual property rights and other related rights arising from use of our products. TAIYO YUDEN grants no license for such rights.
- Please note that unless otherwise agreed in writing, the scope of warranty for our products is limited to the delivered our products themselves and TAIYO YUDEN shall not be in any way responsible for any damages resulting from a fault or defect in our products.
- The contents of this catalog are applicable to our products which are purchased from our sales offices or authorized distributors (hereinafter "TAIYO YUDEN' s official sales channel"). Please note that the contents of this catalog are not applicable to our products purchased from any seller other than TAIYO YUDEN' s official sales channel.

# Caution for Export

Some of our products listed in this catalog may require specific procedures for export according to "U.S. Export Administration Regulations", "Foreign Exchange and Foreign Trade Control Law" of Japan, and other applicable regulations. Should you have any questions on this matter, please contact our sales staff.

# TAIYO YUDEN 2017

# **AXIAL LEADED CERAMIC CAPACITORS**



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# CERAMIC CAPACITORS

PARTS NUMBER



6 Capacitance tolerance

Code D-

J-

к—

М-

Z-

Code

Α-

в-

KF

KE NA

В

С

Internal code

Code

 $\Delta\Delta$ 

ΔZ

ΔJ

8 Packaging Code

⑦Lead Configurations

Capacitance tolerance

 $\pm 0.5 pF$ 

 $\pm 5\%$ 

±10%

±20% +80/-20%

Lead Configurations

26mm lead space, ammo pack

52mm lead space, ammo pack

5.0mm pitch formed lead bulk

7.5mm pitch formed lead bulk

Axial lead, bulk

Packaging

Ammo

Bulk

Internal code

Multilayer type (Standard)

Multilayer type (Low voltage type)

(1)Rated voltage

TRated voltage							
Code	Rated voltage[VDC]						
L	10						
E	16						
Т	25						
G	35						
U	50						

②Series name	
Code	Series name
Р	Axial leaded capacitor

(3)Dimensions (L ×  $\phi$  D)

Code	Dimensions $(L \times \phi D)$ [mm]							
025	2.3×2.0 (Multilayer type)							
050	$3.2 \times 2.2$ (Multilayer type)							
075	4.2 × 3.2 (Multilaver type)							

# (4)Temperature characteristics

Code Temperature characteristics								
	СН	0±60(ppm/°C)						
	ΔB	±10%						
	B5	±15%						
	ΔF	+30/-85%						

# (5)Nominal capacitance

Code (example)	Nominal capacitance[pF]					
010	1					
1R2	1.2					
103	10000					

ℜR=Decimal point

# STANDARD EXTERNAL DIMENSIONS / MINIMUM QUANTITY

						Minimum quantity[pcs]				
Туре	L	$\phi$ D		$\phi$ d		Bulk		Taping		
					NA	KF	KE	A-/B-		
Multilaura tura 005	2.3max	2.0max	0.4	$5 \pm 0.05$	1000	4000		5000		
Multilayer type 025	(0.09max)	(0.079max)	(0.01	8±0.002)	1000	4000	_	5000		
Multilaura tura 050	3.2max	2.2max	0.4	5±0.05	1000	3000		3000		
Multilayer type 050	(0.126max)	(0.087max)	(0.01	8±0.002)	1000	3000	_	3000		
Multilayer type 075	4.2max	3.2max	$0.55 \pm 0.05$		1000	_	3000	2000		
Multilayer type 075	(0.165max)	(0.126max)	(0.02	2±0.002)	1000		3000	2000		
							Unit:m	ım(inch)		
	Bulk				Taping	5				
Straight		Formed			Straigh	nt				
NA	KF	KE		A- B-						
					⊇-∏		Π			
					31					
					→Г	$\rightarrow$				
	Pitch: 5.0(0.197)	Pitch : 7.5 (0.)	295)	26(1	.024)	52(2.047)				
						Unit:mm(inch)				

Multilayer 025 type Class 1

Parts number	Rated voltage[V]	Temperature characteristics	Nominal capacitance[pF]	Capacitance tolerance	Q	Insulation resistance $[M\Omega]$ (min.)
UP025CH010D-[] Z	50	CH	1.0	±0.5pF	Q≧400+20C	10,000
UP025CH1R2D-[] Z	50	CH	1.2	±0.5pF	Q≧400+20C	10,000
UP025CH1R5D-[] Z	50	CH	1.5	±0.5pF	Q≧400+20C	10,000
UP025CH1R8D-[] Z	50	CH	1.8	±0.5pF	Q≧400+20C	10,000
UP025CH2R2D-[] Z	50	CH	2.2	±0.5pF	Q≧400+20C	10,000
UP025CH2R7D-[] Z	50	CH	2.7	±0.5pF	Q≧400+20C	10,000
UP025CH3R3D-[] Z	50	CH	3.3	±0.5pF	Q≧400+20C	10,000
UP025CH3R9D-[] Z	50	CH	3.9	±0.5pF	Q≧400+20C	10,000
UP025CH4R7D-[] Z	50	CH	4.7	±0.5pF	Q≧400+20C	10,000
UP025CH5R6K-[] Z	50	CH	5.6	±10%	Q≧400+20C	10,000
UP025CH6R8K-[] Z	50	CH	6.8	±10%	Q≧400+20C	10,000
UP025CH8R2K-[] Z	50	CH	8.2	±10%	Q≧400+20C	10,000
UP025CH100J-[] Z	50	CH	10	±5%	Q≧400+20C	10,000
UP025CH120J-[] Z	50	CH	12	±5%	Q≧400+20C	10,000
UP025CH150J-[] Z	50	CH	15	±5%	Q≧400+20C	10,000
UP025CH180J-[] Z	50	CH	18	±5%	Q≧400+20C	10,000
UP025CH220J-[] Z	50	CH	22	±5%	Q≧400+20C	10,000
UP025CH270J-[] Z	50	CH	27	±5%	Q≧400+20C	10,000
UP025CH330J-[] Z	50	CH	33	±5%	Q≧1000	10,000
UP025CH390J-[] Z	50	CH	39	±5%	Q≧1000	10,000
UP025CH470J-[] Z	50	CH	47	±5%	Q≧1000	10,000
UP025CH560J-[] Z	50	CH	56	±5%	Q≧1000	10,000
UP025CH680J-[] Z	50	CH	68	±5%	Q≧1000	10,000
UP025CH820J-[] Z	50	CH	82	±5%	Q≧1000	10,000
UP025CH101J-[] Z	50	CH	100	±5%	Q≧1000	10,000
UP025CH151J-[] Z	50	CH	150	±5%	Q≧1000	10,000
UP025CH221J-[] Z	50	CH	220	±5%	Q≧1000	10,000
UP025CH331J-[] Z	50	CH	330	±5%	Q≧1000	10,000
UP025CH471J-[] Z	50	CH	470	±5%	Q≧1000	10,000
UP025CH681J-[] Z	50	CH	680	±5%	Q≧1000	10,000
UP025CH102J-[] Z	50	CH	1 000	±5%	Q≧1000	10,000

Please specify the lead configuration code.

# Multilayer 025 type Class 2

Parts number	Rated voltage[V]	Temperature characteristics	Nominal capacitance[pF]	Capacitance tolerance	tan $\delta$	Insulation resistance [MΩ](min.)
UP025 B101K-[] Z	50	В	100	±10%	tanδ≦3.5%	5,000
UP025 B121K-[] Z	50	В	120	±10%	tanδ≦3.5%	5,000
UP025 B151K-[] Z	50	В	150	±10%	tanδ≦3.5%	5,000
UP025 B181K-[] Z	50	В	180	±10%	tanδ≦3.5%	5,000
UP025 B221K-[] Z	50	В	220	±10%	tanδ≦3.5%	5,000
UP025 B271K-[] Z	50	В	270	±10%	tanδ≦3.5%	5,000
UP025 B331K-[] Z	50	В	330	±10%	tanδ≦3.5%	5,000
UP025 B391K-[] Z	50	В	390	±10%	tanδ≦3.5%	5,000
UP025 B471K-[] Z	50	В	470	±10%	tanδ≦3.5%	5,000
UP025 B561K-[] Z	50	В	560	±10%	tanδ≦3.5%	5,000
UP025 B681K-[] Z	50	В	680	±10%	tanδ≦3.5%	5,000
UP025 B821K-[] Z	50	В	820	±10%	tanδ≦3.5%	5,000
UP025 B102K-[] Z	50	В	1 000	±10%	tanδ≦3.5%	5,000
UP025 B122K-🛛 Z 🛛 ★	50	В	1 200	±10%	tanδ≦3.5%	5,000
UP025 B152K-[] Z	50	В	1 500	±10%	tanδ≦3.5%	5,000
UP025 B222K-[] Z	50	В	2 200	±10%	tanδ≦3.5%	5,000
UP025 B332K-[] Z	50	В	3 300	±10%	tanδ≦3.5%	5,000
UP025 B472K-[] Z	50	В	4 700	±10%	tanδ≦3.5%	5,000
UP025 B682K-[] Z	50	В	6 800	±10%	tanδ≦3.5%	5,000
UP025 B103K-[] Z	50	В	10 000	±10%	tanδ≦3.5%	5,000
UP025 B153K-🛛 Z 🛛 🖈	50	В	15 000	±10%	tanδ≦3.5%	5,000
UP025 B223K-[] Z	50	В	22 000	±10%	tanδ≦3.5%	5,000
UP025 B333K-[] Z	50	В	33 000	±10%	tanδ≦3.5%	5,000
UP025 B473K-[] Z	50	В	47 000	±10%	tanδ≦5.0%	1,000
UP025 B683K-[] Z	50	В	68 000	±10%	tanδ≦5.0%	1,000
UP025 B104K-[] Z	50	В	100 000	±10%	tanδ≦5.0%	1,000
EP025 B224K-[] Z	16	В	220 000	±10%	tanδ≦5.0%	500
EP025 B474K-[] Z	16	В	470 000	±10%	tanδ≦5.0%	200
EP025 B105K-[] Z	16	В	1 000 000	±10%	tanδ≦7.5%	100
UP025B5105K-[] Z	50	B5	1 000 000	±10%	tanδ≦12.5%	100
UP025 F103Z-[] Z	50	F	10 000	+80/-20%	tanδ≦7.5%	1,000
UP025 F223Z-[] Z	50	F	22 000	+80/-20%	tanδ≦7.5%	1,000
UP025 F473Z-[] Z	50	F	47 000	+80/-20%	tanδ≦7.5%	1,000
UP025 F104Z-[] Z	50	F	100 000	+80/-20%	tanδ≦7.5%	1,000
EP025 F224Z-[] Z 🛛 🖈	16	F	220 000	+80/-20%	tanδ≦10.0%	500
EP025 F474Z-[] Z 🛛 🖈	16	F	470 000	+80/-20%	tanδ≦10.0%	500
EP025 F105Z-[] Z 🛛 🖈	16	F	1 000 000	+80/-20%	tanδ≦17.5%	250
EP025 B122M-[] J 🛛 ★	16	В	1 200	±20%	tanδ≦3.5%	5,000
EP025 B152M-🛛 J 🛛 ★	16	В	1 500	±20%	tanδ≦3.5%	5,000
EP025 B182M-🛛 J 🛛 ★	16	В	1 800	±20%	tanδ≦3.5%	5,000
EP025 B222M-[] J 🛛 🛨	16	В	2 200	±20%	tanδ≦3.5%	5,000
EP025 B272M-[] J 🛛 🛨	16	В	2 700	±20%	tanδ≦3.5%	5,000
EP025 B332M-[] J 🛛 ★	16	В	3 300	±20%	tanδ≦3.5%	5,000
EP025 B392M-[] J 🛛 🛨	16	В	3 900	±20%	tanδ≦3.5%	5,000
EP025 B472M-[] J 🛛 ★	16	В	4 700	±20%	tanδ≦3.5%	5,000
EP025 B562M-[] J 🛛 🛧	16	В	5 600	±20%	tanδ≦3.5%	5,000
EP025 B682M-[] J 🛛 ★	16	В	6 800	±20%	tanδ≦3.5%	5,000
EP025 B822M-[] J 🛛 ★	16	В	8 200	±20%	tanδ≦3.5%	5,000
Please specify the lead conf	iguration code.					

Please specify the lead configuration code.

★ : Option

PARTS NUMBER \* All the Axial leaded capacitor of Catalog Lineup are Compliance RoHS.

Parts number	Rated voltage[V]	Temperature characteristics	Nominal capacitance[pF]	Capacitance tolerance	tan δ	Insulation resistance $[M\Omega]$ (min.)
EP025 B103M-[] J 🛛 ★	16	В	10 000	±20%	tanδ≦3.5%	5,000
EP025 B123M-[] J 🛛 🛨	16	В	12 000	±20%	tanδ≦3.5%	5,000
EP025 B153M-[] J 🛛 🖈	16	В	15 000	±20%	tanδ≦3.5%	5,000
EP025 B183M-[] J 🛛 🖈	16	В	18 000	±20%	tanδ≦3.5%	5,000
EP025 B223M-[] J 🛛 🖈	16	В	22 000	±20%	tanδ≦3.5%	5,000
TP025 F103Z-[] J 🛛 ★	25	F	10 000	+80/-20%	tanδ≦7.5%	1,000
TP025 F223Z-[] J 🛛 ★	25	F	22 000	+80/-20%	tanδ≦7.5%	1,000
TP025 F473Z-[] J 🛛 ★	25	F	47 000	+80/-20%	tanδ≦7.5%	1,000

☐ Please specify the lead configuration code.
 ★ : Option

Multilayer 050 type Class 1

Parts number		Rated voltage[V]	Temperature characteristics	Nominal capacitance[pF]	Capacitance tolerance	Q	Insulation resistance $[M\Omega]$ (min.)
UP050CH220J-[] Z		50	СН	22	±5%	Q≧400+20C	10,000
UP050CH240J-[] Z	×	50	СН	24	±5%	Q≧400+20C	10,000
UP050CH270J-[] Z		50	СН	27	±5%	Q≧400+20C	10,000
UP050CH300J-[] Z	*	50	СН	30	±5%	Q≧1000	10,000
UP050CH330J-[] Z		50	CH	33	±5%	Q≧1000	10,000
UP050CH360J-[] Z	*	50	CH	36	±5%	Q≧1000	10,000
UP050CH390J-[] Z		50	CH	39	±5%	Q≧1000	10,000
UP050CH430J-[] Z	*	50	CH	43	±5%	Q≧1000	10,000
UP050CH470J-[] Z		50	CH	47	±5%	Q≧1000	10,000
UP050CH510J-[] Z	*	50	CH	51	±5%	Q≧1000	10,000
UP050CH560J-[] Z	*	50	CH	56	±5%	Q≧1000	10,000
UP050CH620J-[] Z	*	50	CH	62	±5%	Q≧1000	10,000
UP050CH680J-[] Z		50	CH	68	±5%	Q≧1000	10,000
UP050CH750J-[] Z	*	50	CH	75	±5%	Q≧1000	10,000
UP050CH820J-[] Z	*	50	CH	82	±5%	Q≧1000	10,000
UP050CH910J-[] Z	*	50	CH	91	±5%	Q≧1000	10,000
UP050CH101J-[] Z		50	CH	100	±5%	Q≧1000	10,000
UP050CH111J-[] Z	*	50	CH	110	±5%	Q≧1000	10,000
UP050CH121J-[] Z	*	50	CH	120	±5%	Q≧1000	10,000
UP050CH131J-[] Z	*	50	CH	130	±5%	Q≧1000	10,000
UP050CH151J-[] Z		50	CH	150	±5%	Q≧1000	10,000
UP050CH161J-[] Z	*	50	CH	160	±5%	Q≧1000	10,000
UP050CH181J-[] Z	*	50	CH	180	±5%	Q≧1000	10,000
UP050CH201J-[] Z	*	50	CH	200	±5%	Q≧1000	10,000
UP050CH221J-[] Z		50	CH	220	±5%	Q≧1000	10,000
UP050CH241J-[] Z	*	50	CH	240	±5%	Q≧1000	10,000
UP050CH271J-[] Z	*	50	CH	270	±5%	Q≧1000	10,000
UP050CH301J-[] Z	*	50	CH	300	±5%	Q≧1000	10,000
UP050CH331J-[] Z		50	CH	330	±5%	Q≧1000	10,000
UP050CH361J-[] Z	*	50	СН	360	±5%	Q≧1000	10,000
UP050CH391J-[] Z	*	50	СН	390	±5%	Q≧1000	10,000
UP050CH431J-[] Z	*	50	СН	430	±5%	Q≧1000	10,000
UP050CH471J-[] Z		50	CH	470	±5%	Q≧1000	10,000
UP050CH511J-[] Z	*	50	СН	510	±5%	Q≧1000	10,000
UP050CH561J-[] Z	*	50	СН	560	±5%	Q≧1000	10,000
UP050CH621J-[] Z	*	50	СН	620	±5%	Q≧1000	10,000
UP050CH681J-[] Z		50	СН	680	±5%	Q≧1000	10,000
UP050CH751J-[] Z	*	50	СН	750	±5%	Q≧1000	10,000
UP050CH821J-[] Z	*	50	СН	820	±5%	Q≧1000	10,000
UP050CH911J-[] Z	*	50	СН	910	±5%	Q≧1000	10,000
UP050CH102J-[] Z		50	CH	1 000	±5%	Q≧1000	10,000

• Please specify the lead configuration code.

★ : Option

### PARTS NUMBER \* All the Axial leaded capacitor of Catalog Lineup are Compliance RoHS

Parts number		Rated voltage[V]	Temperature characteristics	Nominal capacitance[pF]	Capacitance tolerance	tan δ	Insulation resistance [MΩ] (min.)
2050 B122K-[] Z	*	50	В	1 200	±10%	tanδ≦3.5%	5,000
2050 B152K-[] Z	*	50	В	1 500	±10%	tanδ≦3.5%	5,000
050 B182K-[] Z	*	50	В	1 800	±10%	tanδ≦3.5%	5,000
P050 B222K-[] Z		50	В	2 200	±10%	tanδ≦3.5%	5,000
P050 B272K-[] Z	*	50	В	2 700	±10%	tanδ≦3.5%	5,000
P050 B332K-[] Z		50	В	3 300	±10%	tanδ≦3.5%	5,000
2050 B392K-[] Z	*	50	В	3 900	±10%	tanδ≦3.5%	5,000
P050 B472K-[] Z		50	В	4 700	±10%	tanδ≦3.5%	5,000
P050 B562K-[] Z	*	50	В	5 600	±10%	tanδ≦3.5%	5,000
P050 B682K-[] Z		50	В	6 800	±10%	tanδ≦3.5%	5,000
P050 B822K-[] Z	*	50	В	8 200	±10%	tanδ≦3.5%	5,000
2050 B103K-[] Z		50	В	10 000	±10%	tanδ≦3.5%	5,000
2050 B123K-[] Z	*	50	В	12 000	±10%	tanδ≦3.5%	5,000
P050 B153K-[] Z		50	В	15 000	±10%	tanδ≦3.5%	5,000
2050 B183K-[] Z	*	50	В	18 000	±10%	tanδ≦3.5%	5,000
2050 B223K-[] Z		50	В	2 2000	±10%	tanδ≦3.5%	5,000
P050 B273K-[] Z	*	50	В	27 000	±10%	tanδ≦3.5%	5,000
2050 B333K-[] Z		50	В	33 000	±10%	tanδ≦3.5%	5,000
P050 B393K-[] Z	*	50	В	39 000	±10%	tanδ≦3.5%	5,000
P050 B473K-[] Z		50	В	47 000	±10%	tanδ≦5.0%	1,000
P050 B563K-[] Z	*	50	В	56 000	±10%	tanδ≦5.0%	1,000
P050 B683K-[] Z		50	В	68 000	±10%	tanδ≦5.0%	1,000
P050 B823K-[] Z	*	50	В	82 000	±10%	tanδ≦5.0%	1,000
P050 B104K-[] Z		50	В	100 000	±10%	tanδ≦5.0%	1,000
P050 B224K-[] Z		50	В	220 000	±10%	tanδ≦5.0%	500
P050 B474K-[] Z		50	В	470 000	±10%	tanδ≦5.0%	200
P050 B105K-[] Z		35	В	1 000 000	±10%	tanδ≦5.0%	100
2050 B225K-[] Z		16	В	2 200 000	±10%	tanδ≦7.5%	50
2050 B475K-[] Z		16	В	4 700 000	±10%	tanδ≦12.5%	20
2050 B106K-[] Z		16	В	10 000 000	±10%	tanδ≦12.5%	20
P050 F103Z-[] Z		50	F	10 000	+80/-20%	tanδ≦7.5%	1,000
P050 F223Z-[] Z		50	F	22 000	+80/-20%	tanδ≦7.5%	1,000
P050 F473Z-[] Z		50	F	47 000	+80/-20%	tanδ≦7.5%	1,000
P050 F104Z-[] Z		50	F	100 000	+80/-20%	tanδ≦7.5%	1,000
P050 F224Z-[] Z		50	F	220 000	+80/-20%	tanδ≦10.0%	500
2050 F474Z-[] Z		50	F	470 000	+80/-20%	tanδ≦10.0%	500
P050 F105Z-[] Z		50	F	1 000 000	+80/-20%	tanδ≦15.0%	250
2050 F225Z-[] Z	*	16	F	2 200 000	+80/-20%	tanδ≦15.0%	125
P050 F475Z-[] Z	*	10	F	4 700 000	+80/-20%	tanδ≦17.5%	50
2050 F106Z-	*	10	F	10 000 000	+80/-20%	tanδ≦17.5%	25

★ : Option

# Multilayer 075 type Class 2

Parts number		Rated voltage[V]	Temperature characteristics	Nominal capacitance[pF]	Capacitance tolerance	tan ô	Insulation resistance [MΩ](min.)
UP075 B105K-[]		50	В	1 000 000	±10%	tanδ≦5.0%	100
GP075 B225K-[]		35	В	2 200 000	±10%	tan δ ≦7.5%	50
GP075 B475K-[]		35	В	4 700 000	±10%	tan δ ≦7.5%	20
TP075 B106K-[]		25	В	10 000 000	±10%	tanδ≦12.5%	20
UP075B5225K-[]		50	B5	2 200 000	±10%	tanδ≦12.5%	40
UP075B5475K-[]	*	50	B5	4 700 000	±10%	tanδ≦12.5%	10
GP075B5106K-[]	*	35	B5	10 000 000	±10%	tanδ≦12.5%	10
GP075 F106Z-[]	*	35	F	10 000 000	+80/-20%	tanδ≦17.5%	25

• Please specify the lead configuration code.

★ : Option

# **Axial Leaded Ceramic Capacitors**

# PACKAGING

# 1 Minimum Quantity

Туре	Lead configuration code	Minimum Quantity [pcs]		
туре	Lead computation code	Bulk	Taping	
	A-(1.024  inch wide)		2000(075)	
Multilayer type (075, 050, 025)		—	3000(050)	
	B-(2.047  inches wide)		5000(025)	
	NA	1000		
	KE(075)	3000		
	KF(050)	3000	—	
	KF(025)	4000		

# ②Dimensions of Bulk Products





<b>T</b>	Dimensions (mm)					
Туре	φ D	L	$\phi$ d	l		
Multilayer type	2.0max.	2.3max.	$0.45 \pm 0.05$	20.0min.		
025	(0.079max.)	(0.09max.)	(0.018±0.002)	(0.787min.)		
Multilayer type	2.2max.	3.2max.	$0.45 \pm 0.05$	20.0min.		
050	(0.087max.)	(0.126max.)	(0.018±0.002)	(0.787min.)		
Multilayer type	3.2max.	4.2max.	$0.55 \pm 0.05$	20.0min.		
075	(0.126max.)	(0.165max.)	$(0.022 \pm 0.002)$	(0.787min.)		
				Unit:mm(inch)		

Unit:mm(inch)

# KF/KE configuration



Lead configuration		Dimensions (mm)					
туре	code	φD	L	W	$\phi$ d	l	
Multilayer type	KF	2.0max.	2.3max.	5.0±0.5	0.45±0.05	$6.5 \pm 0.5$	
025		(0.079max.)	(0.09max.)	(0.197±0.020)	(0.018±0.002)	(0.256 $\pm 0.020$ )	
Multilayer type	KF	2.2max.	3.2max.	$5.0 \pm 0.5$	$0.45 \pm 0.05$	$6.5 \pm 0.5$	
050		(0.087max.)	(0.126max.)	(0.197 $\pm 0.020$ )	(0.018 \pm 0.002)	(0.256 $\pm 0.020$ )	
Multilayer type	KE	3.2max.	4.2max.	$7.5 \pm 0.5$	$0.55 \pm 0.05$	$6.5 \pm 0.5$	
075		(0.126max.)	(0.165max.)	(0.295 $\pm 0.020$ )	(0.022 $\pm 0.002$ )	(0.256 $\pm 0.020$ )	
					•	Linit:mm(inch)	

Unit:mm(inch)



# ③Taping Dimensions



Turna		Dimensions (mm)					Minimum insertior
Туре	$\phi$ D	L	а	b	L1-L2	$\phi$ d	pitch
Multilayer type	2.0max.	2.3max.				$0.45 \pm 0.05$	
025	(0.079max.)	(0.09max)				(0.018±0.002)	5.0
Multilayer type	2.2max.	3.2max.	26+0.5/-0	0.8max.	0.5max.	$0.45 \pm 0.05$	(0.197)
050	(0.087max.)	(0.126max.)	(1.024+0.020/-0)	(0.031max.)	(0.020max.)	(0.018±0.002)	
Multilayer type	3.2max.	4.2max.				$0.55 \pm 0.05$	7.5
075	(0.126max.)	(0.165max.)				$(0.022 \pm 0.002)$	(0.295)
							Unit:mm(inch)

B-(a:2.047 inches wide) configuration



Туре		Dimensions (mm)				Minimum insertion	
туре	φD	L	а	b	L1 — L2	$\phi$ d	pitch
Multilayer type	2.0max.	2.3max.				$0.45 \pm 0.05$	
025	(0.079max.)	(0.09max.)				$(0.018 \pm 0.002)$	5.0
Multilayer type	2.2max.	3.2max.	52+2/-1	1.2max.	1.0max.	$0.45 \pm 0.05$	(0.197)
050	(0.087max.)	(0.126max.)	(2.047+0.079/-0.039)	(0.047 max.)	(0.039max.)	$(0.018 \pm 0.002)$	
Multilayer type	3.2max.	4.2max.				$0.55 \pm 0.05$	7.5
075	(0.126max.)	(0.165max.)				$(0.022 \pm 0.002)$	(0.295)
							Unit:mm(inch)

☆Radial taping is available for 075 type (Optional)

# RELIABILITY DATA

1. Operating Tempe	1. Operating Temperature Range				
Specified Value	Class1 (Temperature Compensating)	Multilayer type			
		Multilayer type (Characteristics:B, B5)	-25 to +85°C		
	Class2(High Dielectric)	Multilayer type (Characteristics:F)			

2. Storage Temperature Range			
Specified Value	Class1 (Temperature Compensating)	Multilayer type	
	Close 2 (High Dislostria)	Multilayer type (Characteristics:B, B5)	-25 to +85°C
	Class2(High Dielectric)	Multilayer type (Characteristics:F)	

3. Rate Voltage			
Specified Value	Class1 (Temperature Compensating)	Multilayer type	50VDC
	Class2(High Dielectric)	Multilayer type (Characteristics:B, B5)	16VDC, 25VDC, 35VDC, 50VDC
		Multilayer type (Characteristics:F)	10VDC, 16VDC, 25VDC, 35VDC, 50VDC

4. Withstanding Vol	tage			
Between terminals				
Specified Value	No abnorminality			
Test Methods and	Applied voltage     : Rate Voltage × 3(Class 1)       : Rate Voltage × 2.5(Class 2)			
Remarks	Duration Charge/discharge current			
Between terminals	and body			
Specified Value	No abnorminality			
Test Methods and Remarks	Metal globule method	Applied voltage Duration Charge/Discharge current	: Rate Voltage×2.5 : 1 to 5 sec. : 50mA max.	

Compensating) Multilayer type	10000MΩ min.	
Compensating) Specified Value Class2(High Dielectric) Multilayer type (Characteristics : B, B5)	10000M Ω min.           Rate voltage : 16VDC           1200pF~22000pF(Item△J)           220000pF           470000pF           1000000pF           2200000pF           4700000pF           1000000pF           2200000pF           4700000pF           1000000pF           Rate voltage : 25VDC           1000000pF           Rate voltage : 35VDC           1000000pF           2200000pF           4700000pF           1000000pF           Rate voltage : 50VDC           1000000pF           Rate voltage : 50VDC           100pF~39000pF           47000pF~100000pF           220000pF           47000pF~100000pF           220000pF           470000pF           1000pF           220000pF           470000pF           1000000pF           1000000pF	: 5000 M Ω min     : 500M Ω min     : 200M Ω min     : 200M Ω min     : 100M Ω min     : 20M Ω min     : 20M Ω min     : 20M Ω min     : 100M Ω min     : 10M Ω min     : 10M Ω min     : 100M Ω min     : 100M Ω min     : 100M Ω min     : 200M Ω min      : 200M Ω min      : 200M Ω min      : 200M



			4700000pF	: 10MΩ min
			Rate voltage : 10VDC	
			4700000pF	: 50MΩ min
			1000000pF	: 25MΩ min
			Rate voltage : 16VDC	
			220000pF	: 500MΩ min
			470000pF	: 500MΩ min
			1000000pF	: 250MΩ min
		Multilayer type	2200000pF	: 125MΩ min
		(Characteristics:F)	Rate voltage : 25VDC	
			10000pF~47000pF(Item∆J)	: 1000MΩ min
			Rate voltage : 35VDC	
			1000000pF	: 25MΩ min
			Rate voltage : 50VDC	
			10000pF~100000pF	: 1000MΩ min
			220000pF~470000pF	: 500MΩ min
			1000000pF	: 250M $\Omega$ min
Test Methods and	Applied voltage : Rate vo	oltage		
Remarks	Duration : 60±5 s	sec.		

6. Capacitance			
Specified Value	Class1 (Temperature Compensating)	Multilayer type	±0.5pF ±5% ±10%
	Class2(High Dielectric)	Multilayer type (Characteristics:B, B5	$\pm 10\%, \pm 20\%(Item \Delta J)$
		Multilayer type (Characteristics:F)	+80/-20%
	Measuring frequency	:1MHz±10% (	(Class1 : C≦1000pF)
Test Methods and Remarks	Measuring voltage	: 1kHz±10%       (4)         : 120Hz±10%       (4)         : 1.0±0.5Vrms       (4)         : 1.0±0.2Vrms       (4)         : 1.0±0.2Vrms       (4)	$(Class1 : C > 1000pF)$ $(Class2 : C \le 10 \mu F)$ $(Class2 : C > 10 \mu F)$ $(Class1 : C \le 1000pF)$ $(Class1 : C > 1000pF)$ $(Class2 : C \le 10 \mu F)$ $(Class2 : C > 10 \mu F)$
	Bias application	: None	

7. Q or langent of	of Loss Angle(tanð)			
Class1 (Temperature Compensating)	Class1 (Temperature		30pF or under : Q≧400+20C	
	Multilayer type	33pF or over : $Q \ge 1000$		
		C:Nominal Capacitance[pF]		
		Rate voltage : 16VDC		
		$1200pF \sim 22000pF(Item \Delta J)$	: 3.5% max	
		220000pF~470000pF	: 5.0% max	
		1000000pF~2200000pF	: 7.5% max	
		4700000pF~1000000pF	: 12.5% max	
		Rate voltage : 25VDC		
		1000000pF	: 12.5% max	
	Multilayer type	Rate voltage : 35VDC		
		(Characteristics:B, B5)	1000000pF	: 5.0% max
			2200000pF~4700000pF	: 7.5% max
		1000000pF	: 12.5% max	
Specified Value			Rate voltage : 50VDC	
	Class2(High Dielectric)		100pF~39000pF	: 3.5% max
	Class2(High Dielectric)		47000pF~1000000pF	: 5.0% max
			(100000pF/B5	: 12.5% max)
			2200000pF~4700000pF	: 12.5% max
			Rate voltage : 10VDC	
			4700000pF~1000000pF	: 17.5% max
			Rate voltage : 16VDC	
			220000pF	: 10.0% max
		Multilayer type	470000pF	: 10.0% max
		(Characteristics:F)	1000000pF	: 17.5% max
			2200000pF	: 15.0% max
			Rate voltage : 25VDC	
			10000pF~47000pF(Item∆J)	: 7.5% max
			Rate voltage : 35VDC	



				1000000pF	: 17.5% max
				Rate voltage : 50VDC	
				10000pF~100000pF	: 7.5% max
				220000pF~470000pF	: 10.0% max
				1000000pF	: 15.0% max
	Measuring frequency	:1MHz±10%	(Class1 : C	≦1000pF)	
	:	:1kHz±10%	(Class1:C	>1000pF)	
		:1kHz±10%	(Class2:C	έ≦10μ <b>F</b> )	
Test Methods and		:120Hz±10%	(Class2:C	>10 μF)	
	Measuring voltage	: 1.0±0.5Vrms	(Class1:C	S≦1000pF)	
Remarks	Remarks	: 1.0±0.2Vrms	(Class1:C	>1000pF)	
		: 1.0±0.2Vrms	(Class2:C	c≦10 μF)	
		: 0.5±0.1Vrms	(Class2:C	>10 μF)	
	Bias application	: None			

# 8. Capacitance: Change due to Temperature or Rate of Capacitance Change

# When voltage is not applied

	Class1(Ten Compensat	· · .	Multilayer type		CH:0±60 SL: −350~+1000 [ppm/°C]
Specified Value	Class2(High Dielectric)		Multilayer type (Characteristics:	B, B5)	±10%(B5: ±15%)
			Multilayer type (Characteristics:	F)	+30/-85 %
	Measureme	ent of capacitance at	20°C and 85°C, —	25℃ shall be r	nade to calculate temperature characteristic by the following equation.
	(Class 1)				
	$\frac{(C_{85}-C_{20})}{C_{12}\times \Delta T_{12}} \times 10^{6} (\text{ppm/}^{\circ}\text{C})$				
	$C_{20} \times \Delta T$		<i>,</i> )		
	Change of r	maximum capacitance	e deviation in step 1	l to 5(Class2)	
Test Methods and	Step	Temperatur	re(°C)		
Remarks	1	20			
	2	-25			
	3	20(Reference te	emperature)		
	4	85			
	5	20			
	XIn the B5	5 characteristics is, th	ne Temperatures of	step 1,3, and 5	i are 25°C.

9. Terminal Strengt	h					
Tensile						
	Class1(Temperature Compensating) Multilayer type					
Specified Value	Class? (High Dielectric)		:ilayer type aracteristics∶B, B5)	No abnomalities, such as	cuts or looseness of terminals.	
	Class2(High Dielectric)		:ilayer type aracteristics∶F)			
	Apply the stated tensile force progressively in the direction to draw terminal.					
Test Methods and	Nominal wire diameter[mm	mm] Tensile force[N]		Duration[s]	_	
Remarks	0.45 • 0.55	19.6		5	_	
Torsional						
	Class1 (Temperature Compensating)	Multilayer type				
Specified Value	Class2(High Dielectric)	Multilayer type (Characteristics:B, B5)		No abnomalities, such as	cuts or looseness of terminals.	
		Multilayer type (Characteristics:F)				
	Suspend a weight of specified mass at the end of the terminals and incline the body through the angle of 90 degrees and return it to the initial position.					
Test Methods and	This operation is done over a pe	eriod o	f 5 sec. Then second bend	I in the opposite direction sha	all be made.	
Test Methods and Remarks	Number of bends : 2 times				_	
Remarks	Nominal wire diameter[mm	]	Bending force[N]	Mass weight[kg]		
	0.45•0.55		2.45	0.25	_	

10. Resistance to Vibration				
Specified Value	Class1 (Temperature Compensating)	Multilayer type	Appearance : No significant abnomality Withstanding Voltage : No abnomality	



	Capacitance :	
	4.7pF or under	: Within $\pm 0.5 \text{pF}$
	5.6pF~8.2pF	: Within $\pm 10\%$
	10pF or over	: Within±5%
	Q :	
	30pF or under	: Q≧400+20C
	33pF or over	: Q≧1000
	Insulation resistance	: 10000MΩ min
	C : Nominal Capacitance [pF]	
		mality
		ality
		: Within $\pm 20\%$
		: Within $\pm 10\%$
		. WICHIN ± 10%
		2 E%
		: 3.5% max : 5.0% max
		: 7.5% max
	· · · · · · · · · · · · · · · · · · ·	: 12.5% max
		. E000M ()
		: 5000MΩ min
	-	: 500MΩ min
		: 200MΩ min
		: 100MΩ min
		: 50MΩ min
		: 20MΩ min
	tanδ:	
	1000000pF	: 12.5% max
	Insulation Resistance :	
	1000000pF	: <b>20M</b> Ω min
Multilayer type	Rate Voltage : 35VDC	
(Characteristics:B, B5)	Capacitance : Within $\pm 10\%$	
	tanδ:	
	1000000pF	: 5.0% max
	2200000pF~4700000pF	: 7.5% max
		: 12.5% max
	1000000pF	: 100M $\Omega$ min
		: 50MΩ min
		: 20M $\Omega$ min
		: 10MΩ min
		: 3.5% max
		: 3.5% max : 5.0% max
		: 5.0% max : 12.5% max)
	-	
	· · · · · · · · · · · · · · · · · · ·	: 12.5% max
		5000MO
		: 5000MΩ min
	47000pF~100000pF	: 1000MΩ min
	220000pF	: 500MΩ min
	470000pF	: 200MΩ min
	1000000pF	: 100MΩ min
	2200000pF	: 40MΩ min
	4700000pF	: 10MΩ min
	4700000pF Appearance : No significant abnor	
	· · ·	nality
	Appearance : No significant abnor	nality
	Appearance : No significant abnor Withstanding Voltage : No abnor Rate Voltage : 10VDC	nality ality
Multilaver tvpe	Appearance : No significant abnor Withstanding Voltage : No abnor Rate Voltage : 10VDC Capacitance	nality
Multilayer type (Characteristics:F)	$\begin{array}{c} \mbox{Appearance : No significant abnor}\\ \mbox{Withstanding Voltage : No abnors}\\ \mbox{Rate Voltage : 10VDC}\\ \mbox{Capacitance}\\ \mbox{tan $\delta$ : } \end{array}$	nality ality : Within +80/-20%
	Appearance : No significant abnor         Withstanding Voltage : No abnor         Rate Voltage : 10VDC         Capacitance         tan δ :         4700000pF~1000000pF	nality ality
	Appearance : No significant abnorWithstanding Voltage : No abnorRate Voltage : $10VDC$ Capacitancetan $\delta$ :4700000pF~1000000pFInsulation Resistance :	nality ality : Within +80/-20% : 17.5% max
	Appearance : No significant abnor         Withstanding Voltage : No abnor         Rate Voltage : 10VDC         Capacitance         tan δ :         4700000pF~1000000pF	nality ality : Within +80/-20%
		Insulation Resistance :         1000000pF         Rate Voltage : $35VDC$ Capacitance : Within $\pm 10\%$ tan $\delta$ :         1000000pF         2200000pF~4700000pF         200000pF~4700000pF         1000000pF         Insulation Resistance :         1000000pF         200000pF         Insulation Resistance :         1000000pF         Insulation Resistance :         1000000pF         200000pF         Rate Voltage : $50VDC$ Capacitance : Within $\pm 10\%$ tan $\delta$ :         100pF~39000pF         470000pF~1000000pF         (100000pF/B5         2200000pF~4700000pF         Insulation Resistance :         100pF~39000pF         Insulation Resistance :         100pF~39000pF



			Capacitance	: Within $+80/-20\%$
			tanδ:	
			220000pF	: 10.0% max
			470000pF	: 10.0% max
			1000000pF	: 17.5% max
			2200000pF	: 15.0% max
			Insulation Resistance :	
			220000pF	: 500MΩ min
			470000pF	: 500MΩ min
			100000pF	: 250MΩ min
			2200000pF	: 125MΩ min
			Rate Voltage : 25VDC	
			Capacitance	: Within $+80/-20\%$
			tanδ:	
			10000pF~47000pF(Item∆J)	: 7.5% max
			Insulation Resistance :	
			10000pF~47000pF(Item△J)	: 1000 M $\Omega$ min
			Rate Voltage : 35VDC	
			Capacitance	: Within $+80/-20\%$
			tanδ:	
			1000000pF	: 17.5% max
			Insulation Resistance	
			1000000pF	: 25M $\Omega$ min
			Rate Voltage : 50VDC	
			Capacitance	: Within $+80/-20\%$
			tanδ:	
			10000pF~100000pF	: 7.5% max
			220000pF~470000pF	: 10.0% max
			100000pF	: 15.0% max
			Insulation Resistance :	
			10000pF~100000pF	: 1000MΩ min
			220000pF~470000pF	: 500MΩ min
			100000pF	: 250MΩ min
	According to JIS C 5	101-1	1 .	
	Vibration type	: A		
	Directions	: 2 hrs each in X, Y and Z directions		
Test Methods and	Total	: 6 hrs		
Remarks	Frequency range	: 10 to 55 to 10Hz(1min)		

 Amplitude
 : 1.5mm

 Mountin method
 : Soldering onto the PC board

11. Free Fall				
			Appearance : No significant abnomality Withstanding Voltage : No abnomality	
	Class1 (Temperature Compensating)	Multilayer type	Capacitance 4.7pF or under 5.6pF~8.2pF 10pF or over Q : 30pF or under 33pF or over Insulation resistance C : Nominal Capacitance [pF]	: Within $\pm 0.5 \text{pF}$ : Within $\pm 10\%$ : Within $\pm 5\%$ : Q $\geq 400+20C$ : Q $\geq 1000$ : 10000M $\Omega$ min
Specified Value	Class2(High Dielectric)	Multilayer type (Characteristics∶B, B5)	Appearance: No significant abnomWithstanding Voltage: No abnomaRate Voltage: 16VDCCapacitance:1200pF~22000pF(Item $\Delta$ J)220000pF~1000000pFtan $\delta$ :1200pF~220000pF(Item $\Delta$ J)220000pF~470000pF1000000pF~220000pF4700000pF~1000000pFInsulation resistance:1200pF~22000pF(Item $\Delta$ J)220000pF470000pF~1000000pFInsulation resistance:1200pF~22000pF(Item $\Delta$ J)220000pF470000pF100000pF100000pF100000pF	•



	2200000pF	:50MΩ min
	4700000pF~1000000pF	:20MΩ min
	Rate Voltage:25VDC	
	Capacitance:Within $\pm 10\%$	
	tan δ:	
	1000000pF	:12.5% max
	Insulation resistance:	. 12.0% max
		00140
	1000000pF	:20MΩ min
	Rate Voltage:35VDC	
	Capacitance:Within $\pm 10\%$	
	tan δ:	
	100000pF	:5.0% max
	2200000pF~4700000pF	: 7.5% max
	1000000pF	:12.5% max
	Insulation resistance:	
	1000000pF	: 100M $\Omega$ min
	2200000pF	:50MΩ min
	4700000pF	: 20M Ω min
	1000000pF	:10MΩ min
	Rate Voltage: 50VDC	
	Capacitance:Within $\pm 10\%$	
	tan δ:	
	100pF~39000pF	:3.5% max
	47000pF~1000000pF	: 5.0% max
	(100000pF/B5	: 12.5% max)
	2200000pF~4700000pF	:12.5% max
	Insulation resistance:	
	100pF~39000pF	: 5000M Ω min
	47000pF~100000pF	:1000MΩ min
	220000pF	:500MΩ min
	470000pF	:200MΩ min
	100000pF	:100MΩ min
	2200000pF	:40M $\Omega$ min
	4700000pF	$:10M\Omega$ min
	Appearance:No significant abnomalit	
	Withstanding Voltage: No abnomality	
	Withstanding Voltage: No abnomality	
	Rate Voltage: 10VDC	·Within 190/20%
	Rate Voltage: 10VDC Capacitance	:Within +80/-20%
	Rate Voltage:10VDC Capacitance tan δ:	
	Rate Voltage: 10VDC Capacitance tan δ: 4700000pF~1000000pF	:Within +80/-20% :17.5% max
	Rate Voltage: 10VDC Capacitance tan &: 4700000pF~1000000pF Insulation resistance:	:17.5% max
	Rate Voltage: 10VDC         Capacitance         tan ô:         4700000pF~1000000pF         Insulation resistance:         4700000pF	:17.5% max :50MΩ min
	Rate Voltage: 10VDC         Capacitance         tan ô:         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF	:17.5% max
	Rate Voltage : 10VDC         Capacitance         tan &         4700000pF ~ 10000000pF         Insulation resistance :         4700000pF         1000000pF         Rate Voltage : 16VDC	:17.5% max :50M Ω min :25M Ω min
	Rate Voltage : 10VDC         Capacitance         tan &         4700000pF ~ 10000000pF         Insulation resistance :         4700000pF         1000000pF         Rate Voltage : 16VDC         Capacitance	:17.5% max :50MΩ min
	Rate Voltage: 10VDC         Capacitance         tan &         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF         Rate Voltage: 16VDC         Capacitance         tan &:	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within+80/-20%
	Rate Voltage : 10VDC         Capacitance         tan &         4700000pF ~ 10000000pF         Insulation resistance :         4700000pF         1000000pF         Rate Voltage : 16VDC         Capacitance	:17.5% max :50M Ω min :25M Ω min
	Rate Voltage: 10VDC         Capacitance         tan &         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF         Rate Voltage: 16VDC         Capacitance         tan &:	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within+80/-20%
	Rate Voltage: 10VDC         Capacitance         tan &         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF         Rate Voltage: 16VDC         Capacitance         tan &:         220000pF	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within + 80/-20% : 10.0% max
	Rate Voltage: 10VDC         Capacitance         tan &         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF         Rate Voltage: 16VDC         Capacitance         tan &:         220000pF         470000pF	:17.5% max :50M Ω min :25M Ω min : Within+80/-20% :10.0% max :10.0% max
	Rate Voltage: 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           1000000pF           Capacitance:           4700000pF           200000pF           470000pF           1000000pF           1000000pF           1000000pF           470000pF           100000pF           100000pF	:17.5% max :50M Ω min :25M Ω min : Within+80/-20% :10.0% max :10.0% max :17.5% max
Multilayer type	Rate Voltage : 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance :           4700000pF           1000000pF           1000000pF           Quadratic content of the second of the	: 17.5% max : 50M Ω min : 25M Ω min : Within+80/-20% : 10.0% max : 10.0% max : 17.5% max : 15.0% max
Multilayer type (Characteristics:F)	Rate Voltage: 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan &:           220000pF           1000000pF           1000000pF           Insulation resistance:           220000pF           1000000pF           220000pF           1000000pF           2200000pF           1000000pF           2200000pF           2200000pF           Insulation resistance:           220000pF	: 17.5% max : 50M Ω min : 25M Ω min : Within+80/-20% : 10.0% max : 10.0% max : 17.5% max : 15.0% max : 500M Ω min
	Rate Voltage : 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance :           4700000pF           1000000pF           Rate Voltage : 16VDC           Capacitance           tan &:           220000pF           1000000pF           1000000pF           Insulation resistance :           220000pF           1000000pF           1000000pF           220000pF           470000pF           Insulation resistance :           220000pF           470000pF	: 17.5% max : 50M Ω min : 25M Ω min : Within+80/-20% : 10.0% max : 10.0% max : 10.0% max : 17.5% max : 15.0% max : 500M Ω min : 500M Ω min
	Rate Voltage: 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan &:           220000pF           1000000pF           1000000pF           Insulation resistance:           220000pF           1000000pF           Insulation resistance:           2200000pF           Insulation resistance:           220000pF           Insulation resistance:           220000pF           100000pF	: 17.5% max : 50M Ω min : 25M Ω min : Within+80/-20% : 10.0% max : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 500M Ω min : 500M Ω min : 250M Ω min
	Rate Voltage : 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance :           4700000pF           1000000pF           Rate Voltage : 16VDC           Capacitance           tan &:           220000pF           1000000pF           1000000pF           100000pF           220000pF           1000000pF           220000pF           1000000pF           220000pF           100000pF           220000pF           100000pF           220000pF           200000pF           200000pF           200000pF           200000pF           200000pF           200000pF	: 17.5% max : 50M Ω min : 25M Ω min : Within+80/-20% : 10.0% max : 10.0% max : 10.0% max : 17.5% max : 15.0% max : 500M Ω min : 500M Ω min
	Rate Voltage: 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan &:           220000pF           1000000pF           1000000pF           220000pF           1000000pF           1000000pF           2200000pF           1000000pF           2200000pF           10sulation resistance:           2200000pF           100000pF           200000pF           1000000pF           200000pF           Rate Voltage: 25VDC	: 17.5% max : 50M Ω min : 25M Ω min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 17.5% max : 15.0% max : 500M Ω min : 500M Ω min : 250M Ω min : 250M Ω min : 250M Ω min
	Rate Voltage: 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance:           4700000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan &:           220000pF           1000000pF           1000000pF           220000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           2200000pF           Rate Voltage: 25VDC           Capacitance	: 17.5% max : 50M Ω min : 25M Ω min : Within+80/-20% : 10.0% max : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 500M Ω min : 500M Ω min : 250M Ω min
	Rate Voltage: 10VDC           Capacitance           tan δ:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan δ:           220000pF           1000000pF           1000000pF           20000pF           1000000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           200000pF           1000000pF           2200000pF           Rate Voltage: 25VDC           Capacitance           tan δ:	: 17.5% max : 50M Ω min : 25M Ω min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 17.5% max : 15.0% max : 500M Ω min : 500M Ω min : 250M Ω min
	Rate Voltage: 10VDC           Capacitance           tan &:           4700000pF~1000000pF           Insulation resistance:           4700000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan &:           220000pF           1000000pF           1000000pF           220000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           2200000pF           Rate Voltage: 25VDC           Capacitance	: 17.5% max : 50M Ω min : 25M Ω min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 17.5% max : 15.0% max : 500M Ω min : 500M Ω min : 250M Ω min : 250M Ω min : 250M Ω min
	Rate Voltage: 10VDC           Capacitance           tan δ:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan δ:           220000pF           1000000pF           1000000pF           20000pF           1000000pF           1000000pF           2200000pF           1000000pF           2200000pF           1000000pF           200000pF           1000000pF           2200000pF           Rate Voltage: 25VDC           Capacitance           tan δ:	: 17.5% max : 50M Ω min : 25M Ω min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 17.5% max : 15.0% max : 500M Ω min : 500M Ω min : 250M Ω min
	Rate Voltage: 10VDC           Capacitance           tan δ:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan δ:           220000pF           470000pF           1000000pF           20000pF           1000000pF           2200000pF           10sulation resistance:           2200000pF           10sulation resistance:           2200000pF           100000pF           200000pF           200000pF           Capacitance           tan δ:           100000pF           2200000pF           Rate Voltage: 25VDC           Capacitance           tan δ:           100000pF~47000pF(Item△J)	: 17.5% max : 50M Ω min : 25M Ω min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 17.5% max : 15.0% max : 500M Ω min : 500M Ω min : 250M Ω min
	Rate Voltage: 10VDC           Capacitance           tan δ:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan δ:           220000pF           470000pF           1000000pF           220000pF           1000000pF           2200000pF           1000000pF           2200000pF           100000pF           2200000pF           Insulation resistance:           2200000pF           100000pF           200000pF           100000pF           200000pF           Rate Voltage: 25VDC           Capacitance           tan δ:           10000pF~47000pF(Item△J)           Insulation resistance:	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 500M $\Omega$ min : 500M $\Omega$ min : 250M $\Omega$ min
	Rate Voltage: 10VDC           Capacitance           tan δ:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan δ:           220000pF           1000000pF           20000pF           1000000pF           2200000pF           10sulation resistance:           2200000pF           Insulation resistance:           2200000pF           100000pF           200000pF           Rate Voltage: 25VDC           Capacitance           tan δ:           100000pF           200000pF           Insulation resistance:           100000pF           Capacitance           tan δ:           10000pF~47000pF(Item△J)           Insulation resistance:           10000pF~47000pF(Item△J)           Rate Voltage: 35VDC	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 500M $\Omega$ min : 500M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 125M $\Omega$ min : Within + 80/-20% : 7.5% max : 1000M $\Omega$ min
	Rate Voltage: 10VDC           Capacitance           tan δ:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance           tan δ:           220000pF           470000pF           1000000pF           220000pF           1000000pF           2200000pF           10sulation resistance:           2200000pF           100000pF           200000pF           Rate Voltage: 25VDC           Capacitance           tan δ:           100000pF           200000pF           100000pF           200000pF           Insulation resistance:           100000pF           200000pF           Rate Voltage: 25VDC           Capacitance           tan δ:           10000pF~47000pF (Item△J)           Insulation resistance :           10000pF~47000pF (Item△J)           Rate Voltage: 35VDC           Capacitance           10000pF~47000pF (Item△J)	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 5500M $\Omega$ min : 5500M $\Omega$ min : 250M $\Omega$ min
	Rate Voltage : 10VDCCapacitancetan $\delta$ :4700000pF~1000000pFInsulation resistance :4700000pF1000000pFRate Voltage : 16VDCCapacitancetan $\delta$ :220000pF470000pF1000000pF220000pF100000pF220000pFInsulation resistance :220000pFInsulation resistance :220000pFQuotopF10000pF200000pF200000pF10000pF200000pF100000pF200000pFRate Voltage : 25VDCCapacitancetan $\delta$ :10000pF~47000pF (Item $\Delta$ J)Insulation resistance :10000pF~47000pF (Item $\Delta$ J)Rate Voltage : 35VDCCapacitancetan $\delta$ :	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 5500M $\Omega$ min : 500M $\Omega$ min : 250M $\Omega$ min : 1000M $\Omega$ min : Within + 80/-20%
	Rate Voltage: 10VDCCapacitancetan $\delta$ :4700000pF~1000000pFInsulation resistance:4700000pF1000000pFRate Voltage: 16VDCCapacitancetan $\delta$ :220000pF1000000pF1000000pF20000pFInsulation resistance:220000pFInsulation resistance:220000pFInsulation resistance:220000pFQuotopF100000pF200000pF100000pF200000pFInsulation resistance:10000pF200000pFRate Voltage: 25VDCCapacitancetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Rate Voltage: 35VDCCapacitancetan $\delta$ :10000pF100000pF	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 500M $\Omega$ min : 500M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 125M $\Omega$ min : Within + 80/-20% : 7.5% max : 1000M $\Omega$ min
	Rate Voltage : 10VDCCapacitancetan $\delta$ :4700000pF~1000000pFInsulation resistance :4700000pF1000000pFRate Voltage : 16VDCCapacitancetan $\delta$ :220000pF470000pF1000000pF220000pFInsulation resistance :220000pFInsulation resistance :220000pFInsulation resistance :220000pFQuotopF10000pF20000pF100000pF200000pFInsulation resistance :10000pF~47000pF (Item $\Delta$ J)Insulation resistance :10000pF~47000pF (Item $\Delta$ J)Rate Voltage : 35VDCCapacitancetan $\delta$ :10000pF~47000pF (Item $\Delta$ J)Rate Voltage : 35VDCCapacitancetan $\delta$ :1000000pFInsulation resistance :1000000pFInsulation resistance :	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within+80/-20% : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 5500M $\Omega$ min : 5500M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 125M $\Omega$ min : Within +80/-20% : 7.5% max : 1000M $\Omega$ min : Within +80/-20%
	Rate Voltage: 10VDCCapacitancetan $\delta$ :4700000pF~1000000pFInsulation resistance:4700000pF1000000pFRate Voltage: 16VDCCapacitancetan $\delta$ :220000pF470000pF1000000pF20000pF1000000pF220000pFInsulation resistance:220000pF100000pF200000pF200000pF100000pF200000pF100000pF200000pF100000pF200000pFRate Voltage: 25VDCCapacitancetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Rate Voltage: 35VDCCapacitancetan $\delta$ :1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pF	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 5500M $\Omega$ min : 500M $\Omega$ min : 250M $\Omega$ min : 1000M $\Omega$ min : Within + 80/-20%
	Rate Voltage: 10VDCCapacitancetan $\delta$ :4700000pF~1000000pFInsulation resistance:4700000pF1000000pFRate Voltage: 16VDCCapacitancetan $\delta$ :220000pF470000pF1000000pF220000pF100000pF220000pFInsulation resistance:220000pFInsulation resistance:220000pF100000pF220000pF100000pF200000pF100000pF200000pF100000pF200000pF200000pF100000pF200000pF200000pF100000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Rate Voltage: 35VDCCapacitancetan $\delta$ :100000pFInsulation resistance:100000pFInsulation resistance:1000000pFRate Voltage: 50VDC	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within + 80/-20% : 10.0% max : 10.0% max : 10.0% max : 17.5% max : 500M $\Omega$ min : 500M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : Within + 80/-20% : 7.5% max : 1000M $\Omega$ min : Within + 80/-20% : 7.5% max : 25M $\Omega$ min
	Rate Voltage: 10VDCCapacitancetan $\delta$ :4700000pF~1000000pFInsulation resistance:4700000pF1000000pFRate Voltage: 16VDCCapacitancetan $\delta$ :220000pF470000pF1000000pF20000pF1000000pF220000pFInsulation resistance:220000pF100000pF200000pF200000pF100000pF200000pF100000pF200000pF100000pF200000pFRate Voltage: 25VDCCapacitancetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Rate Voltage: 35VDCCapacitancetan $\delta$ :1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pFInsulation resistance:1000000pF	: 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within+80/-20% : 10.0% max : 10.0% max : 10.0% max : 15.0% max : 5500M $\Omega$ min : 5500M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 125M $\Omega$ min : Within +80/-20% : 7.5% max : 1000M $\Omega$ min : Within +80/-20%



			tan δ: 10000pF~100000pF 220000pF~470000pF 1000000pF	: 7.5% max : 10.0% max : 15.0% max
			Insulation resistance: 10000pF~100000pF 220000pF~470000pF 1000000pF	: 1000M $\Omega$ min : 500M $\Omega$ min : 250M $\Omega$ min
	Drop Test	: Free fall		
Test Methods and	Impact material	: Floor		
Remarks	Height	:1 m		
	Total number of drops	: 5 times		

12. Body Strength			
	Class1 (Temperature Compensating)	Multilayer type	
Specified Value	Class2(High Dielectric)	Multilayer type (Characteristics:B, B5)	No abnomality such as damage.
	Glass2 (High Dielectric)	Multilayer type (Characteristics:F)	
Test Methods and Remarks	Applied force : 19.6N Duration : 5 sec. Speed : Shall atta 0.5R 2.0mm 1.5mm(025type)	ain to specified force in 2 sec.	

13. Solderability				
	Class1 (Temperature Compensating)	Multilayer type		
Specified Value		Multilayer type (Characteristics:B, B5)	At least 75% of lead surface is covered with new solder.	
	Class2(High Dielectric)	Multilayer type (Characteristics:F)		
Test Methods and	Solder temperature : 230±5°C			
Remarks	Duration $: 2\pm 0.$	5 sec.(This test may be applicable	after 6 months storage.)	

		Multilayer type	Appearance:No significant abnom Withstanding Voltage:No abnoma	
	Class1 (Temperature Compensating)		Capacitance change: 8.2pF or under 10pF or over Q: 30pF or under 33pF or over Insulation resistance C: Nominal Capacitance [pF]	:Within ±0.25pF :Within ±2.5% :Q≧400+20C :Q≧1000 :10000MΩ min
Specified Value	Class2(High Dielectric)	Multilayer type (Characteristics: B, B5)	Appearance : No significant abnom Withstanding Voltage : No abnoma Rate Voltage : $16VDC$ Capacitance change : $1200pF \sim 22000pF(Item \Delta J)$ $220000pF \sim 1000000pF$ tan $\delta$ : $1200pF \sim 22000pF(Item \Delta J)$ $220000pF \sim 470000pF$ $1000000pF \sim 220000pF$ $4700000pF \sim 1000000pF$ Insulation resistance : $1200pF \sim 22000pF(Item \Delta J)$ 220000pF	•



	470000pF	: 200M Ω min
	100000pF	:100MΩ min
	2200000pF	:50M $\Omega$ min
	4700000pF~1000000pF	:20MΩ min
	Rate Voltage:25VDC	
	Capacitance change:	
	1000000pF	: Within $\pm 10.0\%$
	tan δ:	
	1000000pF	:12.5% max
	Insulation resistance:	
	1000000pF	: 20M $\Omega$ min
	Rate Voltage: 35VDC	
	Capacitance change:	
	1000000pF~1000000pF	
		:Within ±10.0%
	$\tan \delta$ :	5.0%
	100000pF	:5.0% max
	2200000pF~4700000pF	: 7.5% max
	1000000pF	:12.5% max
	Insulation resistance:	
	1000000pF	:100MΩ min
	2200000pF	: 50M $\Omega$ min
	4700000pF	:20MΩ min
	1000000pF	:10MΩ min
	Rate Voltage:50VDC	
	Capacitance change:	
	100pF~39000pF	: Within $\pm 7.5\%$
	47000pF~1000000pF	:Within $\pm 10.0\%$
	tan δ:	
	100pF~39000pF	: 3.5% max
	47000pF~1000000pF	: 5.0% max
	(100000pF/B5	:12.5% max)
	2200000pF~4700000pF	:12.5% max
	Insulation resistance:	
	100pF~39000pF	: 5000M Ω min
	47000pF~100000pF	:1000MΩ min
	220000pF	: 500M Ω min
	-	
	470000pF	: 200MΩ min
	470000pF 1000000pF	: 200M $\Omega$ min : 100M $\Omega$ min
	1000000pF	: 100M $\Omega$ min
	1000000pF 2200000pF	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min
	1000000pF 2200000pF 4700000pF Appearance:No significant abnom	:100M Ω min :40M Ω min :10M Ω min ality
	1000000pF 2200000pF 4700000pF Appearance:No significant abnom Withstanding Voltage:No abnomal	:100M Ω min :40M Ω min :10M Ω min ality
	1000000pF 2200000pF 4700000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC	:100MΩ min :40MΩ min :10MΩ min ality ity
	1000000pF 2200000pF 4700000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC Capacitance change	:100M Ω min :40M Ω min :10M Ω min ality
	1000000pF 2200000pF 4700000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC Capacitance change tan δ:	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20%
	1000000pF 2200000pF 4700000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC Capacitance change tan $\delta$ : 4700000pF~1000000pF	:100MΩ min :40MΩ min :10MΩ min ality ity
	1000000pF 2200000pF 4700000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC Capacitance change tan $\delta$ : 4700000pF~1000000pF Insulation resistance :	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max
	1000000pF 2200000pF 4700000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC Capacitance change tan $\delta$ : 4700000pF ~ 1000000pF Insulation resistance : 4700000pF	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max : 50M $\Omega$ min
	100000pF 220000pF 470000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC Capacitance change tan &: 4700000pF ~ 1000000pF Insulation resistance : 4700000pF 1000000pF	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max
	100000pF 220000pF 470000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC Capacitance change tan ô: 4700000pF~1000000pF Insulation resistance : 4700000pF 1000000pF Rate Voltage : 16VDC	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min
	100000pF 220000pF 470000pF Appearance:No significant abnom Withstanding Voltage:No abnomal Rate Voltage:10VDC Capacitance change tan ô: 4700000pF~1000000pF Insulation resistance: 4700000pF 1000000pF Rate Voltage:16VDC Capacitance change	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max : 50M $\Omega$ min
	1000000pF 2200000pF 4700000pF Appearance : No significant abnom Withstanding Voltage : No abnomal Rate Voltage : 10VDC Capacitance change tan ô: 4700000pF~1000000pF Insulation resistance : 4700000pF 1000000pF Rate Voltage : 16VDC Capacitance change tan ô: 4700000pF	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min
	100000pF 220000pF 470000pF Appearance: No significant abnom Withstanding Voltage: No abnomal Rate Voltage: 10VDC Capacitance change tan ô: 4700000pF~1000000pF Insulation resistance: 4700000pF 1000000pF Rate Voltage: 16VDC Capacitance change tan ô: 220000pF~470000pF	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min : 20% : Within ±20% : 10.0% max
Multilever type	1000000pF           2200000pF           4700000pF           Appearance: No significant abnom           Withstanding Voltage: No abnomal           Rate Voltage: 10VDC           Capacitance change           tan δ:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance change           tan δ:           220000pF~470000pF           1000000pF	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min
Multilayer type (Characteristics : E)	100000pF 220000pF 470000pF Appearance: No significant abnom Withstanding Voltage: No abnomal Rate Voltage: 10VDC Capacitance change tan ô: 4700000pF~1000000pF Insulation resistance: 4700000pF 1000000pF Rate Voltage: 16VDC Capacitance change tan ô: 220000pF~470000pF	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min : 20% : Within ±20% : 10.0% max
Multilayer type (Characteristics:F)	1000000pF           2200000pF           4700000pF           Appearance: No significant abnom           Withstanding Voltage: No abnomal           Rate Voltage: 10VDC           Capacitance change           tan δ:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance change           tan δ:           220000pF~470000pF           1000000pF	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within ±20% : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : Within ±20% : 10.0% max : 17.5% max
	1000000pF           2200000pF           4700000pF           Appearance: No significant abnom           Withstanding Voltage: No abnomal           Rate Voltage: 10VDC           Capacitance change           tan ô:           4700000pF~1000000pF           Insulation resistance:           4700000pF           1000000pF           Rate Voltage: 16VDC           Capacitance change           tan ô:           220000pF~470000pF           1000000pF           220000pF~470000pF           1000000pF	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within ±20% : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : Within ±20% : 10.0% max : 17.5% max
	1000000pF         2200000pF         4700000pF         Appearance: No significant abnom         Withstanding Voltage: No abnomal         Rate Voltage: 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF         Rate Voltage: 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         1000000pF         Insulation resistance :         4700000pF         Insulation resistance :	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within ±20% : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : Within ±20% : 10.0% max : 17.5% max : 15.0% max
	1000000pF         2200000pF         4700000pF         Appearance: No significant abnom         Withstanding Voltage: No abnomal         Rate Voltage: 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF         Capacitance change         tan ô:         220000pF         Rate Voltage: 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         Insulation resistance :         220000pF         Insulation resistance :         220000pF~470000pF	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within ±20% : 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : Within ±20% : 10.0% max : 17.5% max : 15.0% max : 500M $\Omega$ min
	1000000pF         2200000pF         4700000pF         Appearance: No significant abnom         Withstanding Voltage: No abnomal         Rate Voltage: 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF         Rate Voltage: 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         Insulation resistance:         220000pF~470000pF         Insulation resistance:         220000pF~470000pF         Insulation resistance:         220000pF~470000pF         1000000pF	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within ± 20% : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : Within ± 20% : 10.0% max : 17.5% max : 15.0% max : 500M $\Omega$ min : $250M \Omega$ min : $250M \Omega$ min
	1000000pF         2200000pF         4700000pF         Appearance: No significant abnom         Withstanding Voltage: No abnomal         Rate Voltage: 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance:         4700000pF         1000000pF         Rate Voltage: 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         1000000pF         1000000pF         1000000pF         2200000pF         Insulation resistance:         220000pF~470000pF         1000000pF         220000pF~470000pF         1000000pF         220000pF         Rate Voltage: 25VDC	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within $\pm 20\%$ : Within $\pm 20\%$ : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : $25M \Omega$ min : $17.5\%$ max : $10.0\%$ max : $17.5\%$ max : $10.0\%$ max : $17.5\%$ max : $10.0\%$ max : $10.0\%$ max : $10.0\%$ max : $15.0\%$ max : $15.0\%$ max : $15.0\%$ max : $15.0\%$ max : $125M \Omega$ min : $125M \Omega$ min
	100000pF220000pF470000pF470000pFAppearance:No significant abnomWithstanding Voltage:No abnomalRate Voltage:10VDCCapacitance changetan $\delta$ :4700000pF~1000000pFInsulation resistance:4700000pF1000000pFCapacitance changetan $\delta$ :220000pF~470000pF1000000pF100000pF220000pF100000pF220000pFInsulation resistance:220000pFInsulation resistance:220000pFRate Voltage:25VDCCapacitance changeate Voltage:25VDCCapacitance change	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within ± 20% : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : Within ± 20% : 10.0% max : 17.5% max : 15.0% max : 500M $\Omega$ min : $250M \Omega$ min : $250M \Omega$ min
	$\begin{array}{c c} 1000000 \text{pF} \\ 2200000 \text{pF} \\ 4700000 \text{pF} \\ \hline \\ $	: $100M \Omega \min$ : $40M \Omega \min$ : $10M \Omega \min$ ality ity : Within ± 20% : $17.5\% \max$ : $50M \Omega \min$ : $25M \Omega \min$ : Within ± 20% : $10.0\% \max$ : $17.5\% \max$ : $15.0\% \max$ : $15.0\% \max$ : $15.0\% \max$ : $15.0\% \max$ : $15.0\% \max$ : $15.0\% \max$ : $125M \Omega \min$ : $250M \Omega \min$ : $125M \Omega \min$
	$\begin{array}{c c} 1000000 \mbox{PF} \\ 2200000 \mbox{PF} \\ \hline \\ 2200000 \mbox{PF} \\ \hline \\ $	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within $\pm 20\%$ : Within $\pm 20\%$ : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : $25M \Omega$ min : $17.5\%$ max : $10.0\%$ max : $17.5\%$ max : $10.0\%$ max : $17.5\%$ max : $10.0\%$ max : $10.0\%$ max : $10.0\%$ max : $15.0\%$ max : $15.0\%$ max : $15.0\%$ max : $15.0\%$ max : $125M \Omega$ min : $125M \Omega$ min
	$\begin{array}{c c} 1000000 \mbox{PF} \\ 2200000 \mbox{PF} \\ \hline \\ 2200000 \mbox{PF} \\ \hline \\ $	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within $\pm 20\%$ : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : $25M \Omega$ min : $17.5\%$ max : $17.5\%$ max : $10.0\%$ max : $17.5\%$ max : $15.0\%$ max : $15.0\%$ max : $125M \Omega$ min : $125M \Omega$ min : $125M \Omega$ min : $125M \Omega$ min
	100000pF220000pF470000pF470000pFAppearance:No significant abnomWithstanding Voltage:No abnomalRate Voltage:10VDCCapacitance changetan $\delta$ :4700000pF~100000pFInsulation resistance:4700000pF1000000pFRate Voltage:16VDCCapacitance changetan $\delta$ :220000pF~47000pF1000000pF100000pF220000pFInsulation resistance:220000pFInsulation resistance:220000pFRate Voltage:25VDCCapacitance changetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within ± 20% : $17.5\%$ max : $50M \Omega$ min : $25M \Omega$ min : $25M \Omega$ min : $17.5\%$ max : $10.0\%$ max : $17.5\%$ max : $15.0\%$ max : $15.0\%$ max : $15.0\%$ max : $15.0\%$ max : $125M \Omega$ min : $250M \Omega$ min : $250M \Omega$ min : $250M \Omega$ min : $125M \Omega$ min
	100000pF220000pF470000pF470000pFAppearance:No significant abnomWithstanding Voltage:No abnomalRate Voltage:10VDCCapacitance changetan $\delta$ :4700000pF~1000000pFInsulation resistance:4700000pF1000000pFCapacitance changetan $\delta$ :220000pFRate Voltage:16VDCCapacitance changetan $\delta$ :220000pF220000pFInsulation resistance:220000pFInsulation resistance:220000pFRate Voltage:25VDCCapacitance changetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Rate Voltage:35VDC	: 100M $\Omega$ min         : 40M $\Omega$ min         : 10M $\Omega$ min         ality         ity         : Within ±20%         : 17.5% max         : 50M $\Omega$ min         : 25M $\Omega$ min         : 25M $\Omega$ min         : Within ±20%         : 10.0% max         : 15.0% max         : 500M $\Omega$ min         : 250M $\Omega$ min         : 250M $\Omega$ min         : 250M $\Omega$ min         : 250M $\Omega$ min         : 10.0% max         : 125M $\Omega$ min         : Within ±20%         : 7.5% max         : 1000M $\Omega$ min
	100000pF220000pF470000pF470000pFRate Voltage: No abnomalRate Voltage: 10VDCCapacitance changetan $\delta$ :4700000pF~1000000pFInsulation resistance:4700000pF1000000pFCapacitance changetan $\delta$ :220000pFRate Voltage: 16VDCCapacitance changetan $\delta$ :220000pF220000pFInsulation resistance:220000pF100000pF220000pFInsulation resistance:220000pFRate Voltage: 25VDCCapacitance changetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Rate Voltage: 35VDCCapacitance changetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Rate Voltage: 35VDCCapacitance change	: $100M \Omega$ min : $40M \Omega$ min : $10M \Omega$ min ality ity : Within $\pm 20\%$ : 17.5% max : $50M \Omega$ min : $25M \Omega$ min : $25M \Omega$ min : $17.5\%$ max : $17.5\%$ max : $10.0\%$ max : $17.5\%$ max : $15.0\%$ max : $15.0\%$ max : $125M \Omega$ min : $125M \Omega$ min : $125M \Omega$ min : $125M \Omega$ min
	$100000pF$ $220000pF$ $470000pF$ $470000pF$ Appearance:No significant abnom Withstanding Voltage:No abnomal Rate Voltage:10VDC Capacitance change tan $\delta$ : $4700000pF \sim 1000000pF$ Insulation resistance: $4700000pF$ Rate Voltage:16VDC Capacitance change tan $\delta$ : $220000pF \sim 47000pF$ Insulation resistance: $220000pF$ Insulation resistance: $220000pF$ Rate Voltage:25VDC Capacitance change tan $\delta$ : $10000pF \sim 47000pF (Item \Delta J)$ Insulation resistance: $10000pF \sim 47000pF (Item \Delta J)$ Rate Voltage:35VDC Capacitance change tan $\delta$ :	: 100M $\Omega$ min : 40M $\Omega$ min : 10M $\Omega$ min ality ity : Within $\pm 20\%$ : 17.5% max : 50M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min : 250M $\Omega$ min : 15.0% max : 15.0% max : 15.0% $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 250M $\Omega$ min : 125M $\Omega$ min : 125M $\Omega$ min : 125M $\Omega$ min : 1000M $\Omega$ min : Within $\pm 20\%$
	100000pF220000pF470000pF470000pFRate Voltage: No abnomalRate Voltage: 10VDCCapacitance changetan $\delta$ :4700000pF~1000000pFInsulation resistance:4700000pF1000000pFCapacitance changetan $\delta$ :220000pFRate Voltage: 16VDCCapacitance changetan $\delta$ :220000pF~47000pF1000000pFInsulation resistance:220000pF220000pFInsulation resistance:220000pFInsulation resistance:220000pFRate Voltage: 25VDCCapacitance changetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Insulation resistance:10000pF~47000pF(Item $\Delta$ J)Rate Voltage: 35VDCCapacitance changetan $\delta$ :10000pF~47000pF(Item $\Delta$ J)Rate Voltage: 35VDCCapacitance change	: 100M $\Omega$ min         : 40M $\Omega$ min         : 10M $\Omega$ min         ality         ity         : Within ±20%         : 17.5% max         : 50M $\Omega$ min         : 25M $\Omega$ min         : 25M $\Omega$ min         : Within ±20%         : 10.0% max         : 15.0% max         : 500M $\Omega$ min         : 250M $\Omega$ min         : 250M $\Omega$ min         : 250M $\Omega$ min         : 250M $\Omega$ min         : 10.0% max         : 125M $\Omega$ min         : Within ±20%         : 7.5% max         : 1000M $\Omega$ min



			Insulation resistance:	
			1000000pF	:25MΩ min
			Rate Voltage: 50VDC	
			Capacitance change:	
			10000pF~100000pF	: Within 20.0%
			tan δ:	
			10000pF~100000pF	: 7.5% max
			220000pF~470000pF	:10.0% max
			100000pF	:15.0% max
			Insulation resistance:	
			10000pF~100000pF	:1000MΩ min
			220000pF~470000pF	: 500M $\Omega$ min
			1000000pF	:250MΩ min
	Solder temperature	: 270±5°C		
	Duration	: 5±0.5 sec.		
	Immersed conditions		with t=1.6mm, hole=1.0mm diameter)	
Test Methods and	Preconditioning	: 1 hr of preconditioning at 15	$10 + 0/-10^{\circ}$ C followed by $48 \pm 4$ hrs of	of recovery under the standard
Remarks		condition.		
	Recovery	: Recovery for the following p	eriod under the standard condition afte	r the test.
		$24\pm2$ hrs(Class 1)		
		$48\pm4$ hrs(Class 2)		

15. Resistance to S	Solvent		
	Class1(Temperature Compensating)	Multilayer type	
Specified Value	Class2(High Dielectric)	Multilayer type (Characteristics:B, B5)	No significant abnormality in appearance and legible marking.
		Multilayer type (Characteristics:F)	
	According to JIS C 5101-1		
Test Methods and	Type of test	: Method 1	
Remarks	Solvent temperature	: 20 to 25°C	
Remarks	Duration	: 30±5 sec.	
	Solvent Type	: A in Table 23, Isopropyl alcohol	

			Appearance: No significant abnom	•
			Withstanding Voltage: No abnoma	lity
			Capacitance change:	
			8.2pF or under	:Within $\pm 0.5 \text{pF}$
	Class1 (Temperature		10pF or over	:Within $\pm 5.0\%$
	Compensating)	Multilayer type	Q:	
			8.2pF or under	:Q≧200+10C
			10pF~30pF	:Q≧275+2.5C
			33pF or over	:Q≧350
			Insulation resistance	:1000MΩ min
			C : Nominal Capacitance [pF]	
			Appearance:No significant abnom	nality
		Multilayer type	Withstanding Voltage: No abnomality	
			Rate voltage: 16VDC	
			Capacitance change:	
Specified Value			$1200 pF \sim 22000 pF(Item \Delta J)$	:Within $\pm 12.5\%$
opeemed value			220000pF~10000000pF	:Within ±15.0%
			tan δ:	
			1200pF <b>~</b> 22000pF(Item∆J)	:5.0% max
			220000pF~470000pF	: 7.5% max
			100000pF~2200000pF	:10.0% max
	Class2(High Dielectric)		4700000pF~1000000pF	:22.5% max
		(Characteristics:B, B5)	Insulation resistance:	
			1200pF <b>~</b> 22000pF(Item∆J)	:1000M Ω min
			220000pF	:125MΩ min
			470000pF	:50M $\Omega$ min
			100000pF	:25MΩ min
			2200000pF	:12.5MΩ min
			4700000pF~1000000pF	:5M $\Omega$ min
			Rate voltage: 25VDC	
			Capacitance change:	
			1000000pF	: Within $\pm 15.0\%$



r	1		
		tan δ:	
		1000000pF	:15.0% max
		Insulation resistance: 10000000pF	:5M $\Omega$ min
		Rate voltage: 35VDC	
		Capacitance change:	
		100000pF	:Within $\pm 15.0\%$
		2200000pF~4700000pF	:Within $\pm 15.0\%$
		1000000pF	:Within $\pm 15.0\%$
		tan δ:	
		100000pF	: 7.5% max
		2200000pF~4700000pF	:10.0% max
		1000000pF Insulation resistance:	:22.5% max
		1000000pF	: 50M $\Omega$ min
		2200000pF	$25M\Omega$ min
		4700000pF~10000000pF	:5MΩ min
		Rate voltage:50VDC	
		Capacitance change:	
		100pF~39000pF	:Within $\pm 12.5\%$
		47000pF~4700000pF	: Within $\pm 15.0\%$
		(1000000pF/B5 tan δ:	:Within $\pm 22.5\%$ )
		tan 0: 100pF~39000pF	:5.0% max
		47000pF~100000pF	: 7.5% max
		(100000pF/B5	: Within $\pm 17.5\%$ )
		2200000pF~47000000pF	: 22.5% max
		Insulation resistance:	
		100pF~39000pF	:1000M Ω min
		47000pF~100000pF	: 500M Ω min
		220000pF	: 250M Ω min
		470000pF 1000000pF	:100MΩ min :50MΩ min
		2200000pF	$20M\Omega$ min
		4700000pF	:5MΩ min
		Appearance: No significant abnom	ality
		Appearance:No significant abnom Withstanding Voltage:No abnomal	-
			-
		Withstanding Voltage : No abnomal Rate voltage : 10VDC Capacitance change	-
		Withstanding Voltage : No abnomal Rate voltage : 10VDC Capacitance change tan &	:Within ±30.0%
		Withstanding Voltage : No abnomali Rate voltage : 10VDC Capacitance change tan &: 4700000pF~1000000pF	ity
		Withstanding Voltage : No abnomal Rate voltage : 10VDC Capacitance change tan δ: 4700000pF~1000000pF Insulation resistance :	:Within ±30.0% :20.0% max
		Withstanding Voltage : No abnomali Rate voltage : 10VDC Capacitance change tan &: 4700000pF~1000000pF Insulation resistance : 4700000pF	:Within ±30.0% :20.0% max :10MΩ min
		Withstanding Voltage : No abnomali Rate voltage : 10VDC Capacitance change tan ô: 4700000pF~1000000pF Insulation resistance : 4700000pF 10000000pF	:Within ±30.0% :20.0% max
		Withstanding Voltage : No abnomali Rate voltage : 10VDC Capacitance change tan &: 4700000pF~1000000pF Insulation resistance : 4700000pF	:Within ±30.0% :20.0% max :10MΩ min
		Withstanding Voltage : No abnomali         Rate voltage : 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance :         4700000pF         1000000pF         Rate voltage : 16VDC	:Within ±30.0% :20.0% max :10MΩ min :5MΩ min
		Withstanding Voltage : No abnomali         Rate voltage : 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance :         4700000pF         1000000pF         Rate voltage : 16VDC         Capacitance change         tan ô:         220000pF~470000pF	ity : Within ± 30.0% : 20.0% max : 10M Ω min : 5M Ω min : Within ± 30.0% : 15.0% max
		Withstanding Voltage : No abnomali         Rate voltage : 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance :         4700000pF         1000000pF         Rate voltage : 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         1000000pF	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max
		Withstanding Voltage : No abnomali         Rate voltage : 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance :         4700000pF         1000000pF         Rate voltage : 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         220000pF~470000pF         220000pF	ity : Within ± 30.0% : 20.0% max : 10M Ω min : 5M Ω min : Within ± 30.0% : 15.0% max
	Multilayer tyre	Withstanding Voltage : No abnomali         Rate voltage : 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance :         4700000pF         1000000pF         Rate voltage : 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         1000000pF         1000000pF         Insulation resistance :	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max
	Multilayer type (Characteristics : E)	Withstanding Voltage : No abnomali         Rate voltage : 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance :         4700000pF         1000000pF         Rate voltage : 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         1000000pF         220000pF~470000pF         1000000pF         220000pF         Insulation resistance :         220000pF	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 100M $\Omega$ min
	Multilayer type (Characteristics:F)	Withstanding Voltage : No abnomali         Rate voltage : 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance :         4700000pF         1000000pF         Rate voltage : 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         1000000pF         220000pF~470000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF         1000000pF	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan ô:4700000pF~1000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan ô:220000pF~470000pF1000000pF220000pFInsulation resistance :220000pFInsulation resistance :220000pF470000pF470000pF470000pF470000pF470000pF	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min
		Withstanding Voltage : No abnomali         Rate voltage : 10VDC         Capacitance change         tan ô:         4700000pF~1000000pF         Insulation resistance :         4700000pF         1000000pF         Rate voltage : 16VDC         Capacitance change         tan ô:         220000pF~470000pF         1000000pF         1000000pF         220000pF~470000pF         Insulation resistance :         220000pF         Insulation resistance :         220000pF         100000pF         100000pF         100000pF         100000pF	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomali Rate voltage : 10VDC Capacitance change tan ô: 4700000pF~10000000pF Insulation resistance : 4700000pF Rate voltage : 16VDC Capacitance change tan ô: 220000pF~470000pF 1000000pF 220000pF Insulation resistance : 220000pF 470000pF 100000pF 220000pF 220000pF 470000pF	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~1000000pFInsulation resistance :4700000pF1000000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF200000pFInsulation resistance :220000pF220000pFInsulation resistance :220000pFRate voltage : 25VDCCapacitance changetan $\delta$	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~1000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF220000pFInsulation resistance :220000pF1000000pF20000pFInsulation resistance :220000pFRate voltage : 25VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~1000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF220000pFInsulation resistance :220000pF100000pF20000pFInsulation resistance :220000pFRate voltage : 25VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Insulation resistance :	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~1000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF220000pF1000000pF220000pF100000pF220000pFInsulation resistance :220000pF100000pF20000pFRate voltage : 25VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Insulation resistance :10000pF~47000pF (Item $\Delta$ J)	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~10000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF220000pF~470000pFInsulation resistance :220000pF200000pFInsulation resistance :220000pFQuotopF100000pF200000pFInsulation resistance :220000pF100000pF200000pFInsulation resistance :200000pFInsulation resistance :10000pF~47000pF(Item $\Delta$ J)Insulation resistance :10000pF~47000pF(Item $\Delta$ J)Rate voltage : 35VDCRate voltage : 35VDC	ity : Within $\pm 30.0\%$ : 20.0% max : 10M Ω min : 5M Ω min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M Ω min : 50M Ω min : 25M Ω min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~10000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF220000pFInsulation resistance :220000pF1000000pF200000pFInsulation resistance :220000pFQuotopF100000pF200000pFInsulation resistance :220000pFQuotopF100000pF200000pFInsulation resistance :200000pFRate voltage : 25VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Insulation resistance :10000pF~47000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance change	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~10000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF220000pF~470000pFInsulation resistance :220000pF200000pFInsulation resistance :220000pFQuotopF100000pF200000pFInsulation resistance :220000pF100000pF200000pFInsulation resistance :200000pFInsulation resistance :10000pF~47000pF(Item $\Delta$ J)Insulation resistance :10000pF~47000pF(Item $\Delta$ J)Rate voltage : 35VDCRate voltage : 35VDC	ity : Within $\pm 30.0\%$ : 20.0% max : 10M Ω min : 5M Ω min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M Ω min : 50M Ω min : 25M Ω min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~10000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF20000pFInsulation resistance :220000pF20000pFInsulation resistance :220000pF20000pFRate voltage : 25VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Insulation resistance :10000pF~47000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance changetan $\delta$ :	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~10000000pFInsulation resistance :4700000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pFInsulation resistance :220000pF~470000pFInsulation resistance :220000pF1000000pF200000pFInsulation resistance :220000pFQuotopF100000pF200000pFInsulation resistance :220000pFQuotopF100000pF200000pFInsulation resistance :200000pFRate voltage : 25VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Insulation resistance :10000pF~47000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance changetan $\delta$ :100000pF	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~10000000pFInsulation resistance :4700000pF10000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF220000pF~470000pF1000000pF220000pFInsulation resistance :220000pF200000pFRate voltage : 25VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Insulation resistance :10000pF~47000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance changetan $\delta$ :100000pFInsulation resistance :10000pF~47000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance changetan $\delta$ :1000000pFInsulation resistance :	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min
		Withstanding Voltage : No abnomaliRate voltage : 10VDCCapacitance changetan $\delta$ :4700000pF~10000000pFInsulation resistance :4700000pF1000000pFRate voltage : 16VDCCapacitance changetan $\delta$ :220000pF~470000pF1000000pF220000pF~470000pF1000000pF220000pF1000000pF200000pF200000pFCapacitance changetan $\delta$ :1000000pF200000pFRate voltage : 25VDCCapacitance changetan $\delta$ 10000pF~47000pF (Item $\Delta$ J)Insulation resistance :10000pF~47000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance changetan $\delta$ :100000pFInsulation resistance :10000pF~1000pF (Item $\Delta$ J)Rate voltage : 35VDCCapacitance changetan $\delta$ :1000000pFInsulation resistance :1000000pFInsulation resistance :1000000pFInsulation resistance :1000000pFInsulation resistance :1000000pFInsulation resistance :1000000pF	ity : Within $\pm 30.0\%$ : 20.0% max : 10M $\Omega$ min : 5M $\Omega$ min : Within $\pm 30.0\%$ : 15.0% max : 22.5% max : 17.5% max : 17.5% max : 100M $\Omega$ min : 50M $\Omega$ min : 25M $\Omega$ min



				10000pF~100000pF	:Within $\pm 30.0\%$	
				tan δ:		
				10000pF~100000pF	:12.5% max	
				220000pF~470000pF	:15.0% max	
				1000000pF	:17.5% max	
				Insulation resistance:		
				10000pF~100000pF	: 500M $\Omega$ min	
				220000pF~470000pF	: 250M $\Omega$ min	
				1000000pF	: 50M $\Omega$ min	
	Conditions for	or 1 cycle				
	Step	Temperature[°C]	Duration[min.]			
	1	Room temperature	Within 3			
	2	-25+0/-3	30±3			
	3	Room temperature	Within 3			
Test Methods and	4	+85+3/-0	30±3			
Remarks	5	Room temperature	Within 3			
	Number of c	vcles : 5				
	Precondition	ing : 1 hr of preconditio	ning at 150 +0/-10°0	C followed by $48\pm4$ hrs of recov	very under the standard condition.	
	Recovery : Recovery for the following period under the standard condition after the removal from test chamber.					
	24±2 hrs( Class 1)					
			s 2)			

T7. Damp Heat(ste	ady state)	I	I	
			Appearance: No significant abnomal	ty
			Withstanding Voltage: No abnomality	/
			Capacitance change:	
			8.2pF or under	:Within ±0.5pF
			10pF or over	:Within $\pm 5.0\%$
	Class1 (Temperature	Multilayer type	Q:	
	Compensating)		8.2pF or under	:Q≧200+10C
			10pF~30pF	:Q≧275+2.5C
			33pF or over	:Q≧350
			Insulation resistance	:1000MΩ min
			C : Nominal Capacitance [pF]	
			Appearance: No significant abnomal	+
			Withstanding Voltage: No abnomality	•
			Rate voltage: 16VDC	
			Capacitance change:	
			1200pF~22000pF(Item△J)	:Within $\pm 12.5\%$
			220000pF~1000000pF	:Within ±15.0%
			tan ô:	
			$1200 \text{pF} \sim 22000 \text{pF} (\text{Item} \Delta \text{J})$	:5.0% max
			220000pF~470000pF	: 7.5% max
			100000pF~2200000pF	:10.0% max
			4700000pF~1000000pF	:22.5% max
Specified Value			Insulation resistance:	
			$1200 pF \sim 22000 pF(Item \Delta J)$	:1000MΩ min
			220000pF	:125MΩ min
			470000pF	:50MΩ min
			100000pF	:25MΩ min
		Multilayer type	2200000pF	:12.5MΩ min
	Class2(High Dielectric)	(Characteristics:B, B5)	4700000pF~10000000pF	:5MΩ min
			Rate voltage:25VDC	
			Capacitance change:	
			1000000pF	: Within $\pm 15.0\%$
			tan δ:	
			1000000pF	:15.0% max
			Insulation resistance:	
			1000000pF	:5M $\Omega$ min
			Rate voltage: 35VDC	
			Capacitance change:	
			1000000pF	: Within $\pm 15.0\%$
			2200000pF~4700000pF	:Within $\pm 15.0\%$
			1000000pF	: Within $\pm 15.0\%$
			tan δ:	. Within 10.0/
				:10.0% max
			100000pF 220000pF~470000pF	
			2200000pF~4700000pF	: 10.0% max
	<u> </u>		1000000pF	:22.5% max



			Insulation resistance:	
			1000000pF	:50M $\Omega$ min
			2200000pF	$:25M\Omega$ min
			4700000pF~10000000pF	:5MΩ min
			Rate voltage: 50VDC	
			Capacitance change:	
			100pF~39000pF	:Within $\pm 12.5\%$
			47000pF~4700000pF	:Within $\pm 15.0\%$
			(1000000pF/B5	:Within ±22.5%)
			tan ð:	
			100pF~39000pF	:5.0% max
			47000pF~1000000pF	: 7.5% max
			(100000/B5	:17.5% max)
			2200000pF~4700000pF	:22.5% max
			Insulation resistance:	100014 0
			100pF~39000pF 47000pF~100000pF	: 1000M Ω min : 500M Ω min
			220000pF	:250M Ω min
			470000pF	:100M Ω min
			1000000pF	$:50M \Omega$ min
			2200000pF	$:20M\Omega$ min
			4700000pF	:5M Ω min
			Appearance: No significant abnom	
			Withstanding Voltage: No abnomali	•
			Rate voltage: 10VDC	
			Capacitance change	:Within ±30.0%
			tan ô:	
			4700000pF~1000000pF	:20.0% max
			Insulation resistance:	
			4700000pF	: 10M $\Omega$ min
			1000000pF	:5MΩ min
			Rate voltage:16VDC	
			Capacitance change	:Within ±30.0%
			tan δ:	
			220000pF~470000pF	:15.0% max
			1000000pF	:22.5% max
			2200000pF	:17.5% max
			Insulation resistance:	
			220000pF	:100MΩ min
			470000pF	: 50M $\Omega$ min
			100000pF	: 25M Ω min
			2200000pF	:25MΩ min
		Multilayer type	Rate voltage:25VDC	
		(Characteristics:F)	Capacitance change	:Within $\pm 30\%$
			tanδ:	
			10000pF~47000pF(Item△J)	:12.5% max
			Insulation resistance:	500140
			$\frac{10000 \text{pF} \sim 47000 \text{pF} (\text{Item} \Delta \text{J})}{\text{Pate we have } 25 \text{(}\text{PO})}$	:500MΩ min
			Rate voltage: 35VDC	
			Capacitance change tan δ:	:Within ±30.0%
			tan 0: 10000000pF	:20.0% max
			Insulation resistance:	. 20.0/0 IIIdX
			1000000pF	: 5M $\Omega$ min
			Rate voltage: 50VDC	
			Capacitance change:	
			10000pF~100000pF	:Within $\pm 30.0\%$
			tan ô:	
			10000pF~100000pF	:12.5% max
			220000pF~470000pF	: 15.0% max
			1000000pF	: 17.5% max
			Insulation resistance:	
			10000pF~100000pF	:500MΩ min
			220000pF~470000pF	:250MΩ min
		1	1000000pF	:50M $\Omega$ min
	Temperature : 40±2°C	;		
Test Methods and	Temperature: 40±2°CHumidity: 90 to 95			
Fest Methods and Remarks	Humidity : 90 to 95			



 Recovery	: $24\pm2$ hrs of recovery under the standard condition after the removal from test chamber.
	(Class 1)
	: 1 hr of preconditioning at 150 $+$ 10 $/-0$ °C followed by 48 $\pm$ 4 hrs of recovery under the standard condition after
	the removal from chamber. (Class 2)

18. Loading under	Damp Heat			
			Appearance : No significant abnomali Withstanding Voltage : No abnomality	-
			Capacitance change: 8.2pF or under	:Within $\pm 0.75$ pF
	Class1 (Temperature Compensating)	Multilayer type	10pF or over Q: 30pF or under	:Within $\pm 7.5\%$ :Q $\geq 100 + 10/3*C$
			33pF or over Insulation resistance	:Q≧200 :500MΩ min
			C : Nominal Capacitance [pF]	
			Appearance:No significant abnomali Withstanding Voltage:No abnomality	
			Rate voltage: 16VDC	
			Capacitance change: 1200pF~22000pF(Item△J)	:Within $\pm 12.5\%$
			220000pF~470000pF	:Within $\pm 15.0\%$
			1000000pF~1000000pF tan δ:	:Within ±22.5%
			1200pF~22000pF(Item∆J)	:5.0% max
			220000pF~470000pF	: 7.5% max
			1000000pF~2200000pF 4700000pF~1000000pF	: 10.0% max : 22.5% max
			Insulation resistance:	. 22.5% max
			1200pF~22000pF(Item∆J)	: 500M $\Omega$ min
			220000pF	:50MΩ min
			470000pF 1000000pF	: 25MΩ min : 12.5MΩ min
			2200000pF	: 5.0M Ω min
			4700000pF~1000000pF	:2.5MΩ min
			Rate voltage: 25VDC	
Specified Value			Capacitance change: 10000000pF	:Within $\pm 22.5\%$
			tan δ: 10000000pF	:22.5% max
		Multilayer type	Insulation resistance: 10000000pF	:2.5MΩ min
	Class2(High Dielectric)	(Characteristics: B, B5)	Rate voltage: 35VDC	
			Capacitance change: 1000000pF	: Within $\pm 15.0\%$
			2200000pF	:Within $\pm 15.0\%$
			4700000pF~1000000pF	:Within ±22.5%
			tan δ: 1000000pF	: 10.0% max
			2200000pF~4700000pF	: 10.0% max
			1000000pF	:22.5% max
			Insulation resistance:	10 FM 0
			1000000pF 2200000pF	:12.5MΩ min :5.0MΩ min
			4700000pF~1000000pF	: 2.5M Ω min
			Rate voltage: 50VDC	
			Capacitance change: 100pF~39000pF	:Within $\pm 12.5\%$
			47000pF~1000000pF	:Within $\pm 15.0\%$
			(1000000pF/B5	:Within $\pm 22.5\%$ )
			2200000pF~4700000pF	:Within ±22.5%
			tan δ: 100pF∼39000pF	: 5.0% max
			47000pF~1000000pF	: 7.5% max
			(100000pF/B5	:17.5% max)
			2200000pF~4700000pF	:22.5% max
			Insulation resistance: 100pF~39000pF	: 500M $\Omega$ min
			47000pF~100000pF	:250MΩ min
-				



	:		econditioning at 150+10/-0 °C oval from chamber.(Class 2)	followed by 48±4 hrs of recovery ur	ider the standard condition after
- tomarko	(	(Class 1)	-	condition after the removal from test	
Test Methods and Remarks	Preconditioning :	1 hr of pr	econditioning at 150 $+0/-10$ °	C followed by $48 \pm 4$ hrs of recovery	
To at Matter 1		Rate volta			
		500 + 24			
		: 40±2°C : 90 to 95 %	6 RH		
	<b>-</b> .	40 1 000		1000000pF	:25MΩ min
				220000pF~470000pF	:125MΩ min
				10000pF~100000pF	: 250M $\Omega$ min
				Insulation resistance:	
				100000pF	: 17.5% max
				220000pF~470000pF	: 15.0% max
				10000pF~100000pF	:12.5% max
				10000pF ~ 100000pF tan δ:	.within ±30.0%
				Capacitance change 10000pF~1000000pF	: :Within $\pm 30.0\%$
				Rate voltage: 50VDC	
				1000000pF	: 2.5MΩ min
				Insulation resistance:	A EMO
				1000000pF	:20.0% max
				tan δ:	
				Capacitance change	:Within $\pm 30.0\%$
				Rate voltage:35VDC	
				$\underline{10000pF\sim}47000pF(Item\Delta J)$	: 250MΩ min
				Insulation resistance:	
				10000pF~47000pF(Item∆J)	:12.5% max
			(Characteristics:F)	$\tan \delta$	
			Multilayer type	Capacitance change	:Within ±30.0%
			NA 1111	Rate voltage:25VDC	
				220000pF	:12.5MΩ min
				100000pF	:12.5MΩ min
				470000pF	: 25M Ω min
				Insulation resistance: 220000pF	: 50M $\Omega$ min
				2200000pF	:17.5% max
				1000000pF	: 22.5% max
				220000pF~470000pF	: 15.0% max
				$\tan \delta$ :	15.0%
				Capacitance change	:Within $\pm 30.0\%$
				Rate voltage: 16VDC	
				1000000pF	: 2.5MΩ min
				470000pF	:5MΩ min
				Insulation resistance:	
				4700000pF~1000000pF	:20.0% max
				tan δ:	
				Capacitance change	:Within $\pm 30.0\%$
				Rate voltage: 10VDC	
				Withstanding Voltage: No abnomali	ty
				Appearance: No significant abnoma	ality
				4700000pF	: 2.5MΩ min
				2200000pF	:10MΩ min
				1000000pF	: 12.5M Ω min
				470000pF	:25MΩ min

19. High Temperat	ure Lading Test			
	Class1 (Temperature Compensating)		Appearance:No significant abnomality Withstanding Voltage:No abnomality	
			Capacitance change: 8.2pF or under 10pF or over	:Within $\pm 0.3 pF$ :Within $\pm 3.0\%$
Specified Value		Multilayer type	Q: 8.2pF or under	:Q≧200+10C
			10pF~30pF 33pF or over	:Q≧275+2.5C :Q≧350
			Insulation resistance $:1000M\Omega$ min	:1000MΩ min



		C : Nominal Capacitance [pF]	
		Appearance:No significant abnom	
		Withstanding Voltage:No abnoma	lity
		Rate voltage:16VDC	
		Capacitance change:	
		1200pF~22000pF(Item∆J)	:Within $\pm 12.5\%$
		220000pF~470000pF	:Within $\pm 15.0\%$
		100000pF~1000000pF	:Within $\pm 22.5\%$
		tan δ:	
		1200pF~22000pF(Item△J)	:5.0% max
		220000pF~470000pF	: 7.5% max
		100000pF~220000pF	:10.0% max
		4700000pF~1000000pF	:22.5% max
		Insulation resistance:	
		$1200 \text{pF} \sim 22000 \text{pF} (\text{Item} \Delta \text{J})$	: 1000M $\Omega$ min
		220000pF	: 125M Ω min
			: 50M Ω min
		470000pF	
		100000pF	: 25M Ω min
		2200000pF	:12.5MΩ min
		4700000pF~1000000pF	: 5.0MΩ min
		Rate voltage:25VDC	
		Capacitance change:	
		1000000pF	:Within ±22.5%
		tan δ:	
		1000000pF	:22.5% max
		Insulation resistance:	
		1000000pF	: 5M $\Omega$ min
			. OW JE HIIT
		Rate voltage: 35VDC	
	Marthalles and	Capacitance change:	
	Multilayer type	1000000pF	:Within $\pm 15.0\%$
	(Characteristics:B, B5)	2200000pF	:Within $\pm 15.0\%$
		4700000pF~1000000pF	:Within ±22.5%
		tan δ:	
		1000000pF	:10.0% max
		2200000pF~4700000pF	: 10.0% max
Class2(High Dielectric)		1000000pF	: 22.5% max
		· · · · · · · · · · · · · · · · · · ·	. 22.0/0 IIIdX
		Insulation resistance:	
		100000pF	:25MΩ min
		2200000pF	: 25M Ω min
		4700000pF~1000000pF	:5MΩ min
		Rate voltage: 50VDC	
		Capacitance change:	
		100pF~39000pF	: Within $\pm 12.5\%$
		47000pF~100000pF	:Within $\pm 15.0\%$
		(100000pF/B5	: Within $\pm 22.5\%$ )
		2200000pF~4700000pF	: Within $\pm 22.5\%$
			. Michini <u>– 22.0</u> /0
		tan δ:	
		100pF~39000pF	: 5.0% max
		47000pF~100000pF	: 7.5% max
		(100000/B5	:17.5% max)
		2200000pF~4700000pF	:22.5% max
		Insulation resistance:	
		100pF~39000pF	:1000MΩ min
		47000pF~100000pF	:500MΩ min
		220000pF	: 250M Ω min
		470000pF	: 100M Ω min
		100000pF	$:50M \Omega$ min
		2200000pF	:20MΩ min
		4700000pF	:5MΩ min
		Appearance:No significant abnom	nality
		Withstanding Voltage:No abnoma	lity
		Rate voltage: 10VDC	
		Capacitance change	:Within ±30.0%
	Multilovor ture		. WILHIN 1 50.0%
	Multilayer type	$\tan \delta$	
	(Characteristics:F)	4700000pF~1000000pF	:20.0% max
		Insulation resistance:	
	1	4700000pF	:10MΩ min
		1000000pF	:5MΩ min



			Capacitance change	:Within ±30.0%		
			tan δ:			
			220000pF~470000pF	:15.0% max		
			100000pF	:22.5% max		
			2200000pF	:17.5% max		
			Insulation resistance:			
			220000pF	:100MΩ min		
			470000pF	:50M $\Omega$ min		
			100000pF	: 25M $\Omega$ min		
			2200000pF	: 25M $\Omega$ min		
			Rate voltage: 25VDC			
			Capacitance change	: Within $\pm 30\%$		
			tan ô:			
			10000pF~47000pF(Item∆J)	:10.0% max		
			Insulation resistance:			
			10000pF~47000pF(Item∆J)	: 500M $\Omega$ min		
			Rate voltage: 35VDC			
			Capacitance change	:Within $\pm 30.0\%$		
			tan δ:			
			1000000pF	:20.0% max		
			Insulation resistance:			
			1000000pF	:5M $\Omega$ min		
			Rate voltage: 50VDC			
			Capacitance change:			
			10000pF~100000pF	: Within 30.0%		
			tan 0:			
			10000pF~100000pF	:10.0% max		
			220000pF~470000pF	: 12.5% max		
			1000000pF	: 17.5% max		
			Insulation resistance:			
			10000pF~100000pF	: 500M $\Omega$ min		
			220000pF~470000pF	: 250M Ω min		
			1000000pF	:50M Ω min		
	Temperature	: 85 +3/-0 °C	100000000			
	Duration	1000 + 48/-0 hrs				
	Applied voltage : Rate voltage × 2					
	: Rate voltage $\times$ 1.5 Class 2: R R5 1000000-E(025Ture)					
est Methods and	Class 2: B,B5 1000000pF(025Type)					
emarks	: B,B5 220000pF $\sim$ 10000000pF(050Type, 075Type)					
	Preconditioning : 1 hr of preconditioning at $150 + 10 - 0$ °C followed by $48 \pm 4$ hrs of recovery under the standard condition.					
	Recovery	•	ne standard condition after the removal from test	cnamber.		
		(Class1)	$10-0$ °C followed by $40\pm4$ has of $\cdots$	day the standard soudition often th		
			$\pm 10-0$ °C followed by 48 $\pm 4$ hrs of recovery unc	der the standard condition after t		
-		removal from chamber. (Cla d condition″ referred to herein is o				

Note on standard condition: "standard condition" referred to herein is defined as follows:

5 to 35°C of temperature, 45 to 85% relative humidity, and 86 to 106kPa of air pressure.

When there are questions concerning measurement results:

In order to provide correlation data, the test shall be conducted under condition of  $20\pm 2^{\circ}$ C of temperature, 60 to 70% relative humidity, and 86 to 106kPa of air pressure.Unless otherwise specified, all the tests are conducted under the "standard condition."

Withstanding voltage is also referred to as "voltage proof" under IEC specifications.



# PRECAUTIONS

1. Circuit Design	
Precautions	<ul> <li>Verification of operating environment, electrical rating and performance</li> <li>1. A malfunction in medical equipment, spacecraft, nuclear reactors, etc. may cause serious harm to human life or have severe social ramifications. As such, any capacitors to be used in such equipment may require higher safety and/or reliability considerations and should be clearly differentiated from components used in general purpose applications.</li> <li>Verification of Rated voltage (DC rated voltage)</li> <li>1. The operating voltage for capacitors must always be lower than their rated values. If an AC voltage is loaded on a DC voltage, the sum of the two peak voltages should be lower than the rated value of the capacitor chosen. For a circuit where both an AC and a pulse voltage may be present, the sum of their peak voltages should also be lower than the capacitor's rated voltage.</li> <li>Self-generated heat (Verification of Temperature)</li> <li>1. If the capacitors specified only for DC use are used in AC or pulse circuits, the AC or a pulse current can generate heat inside the capacitor so the self-generated temperature rise should be limited to within 20°C. The surface temperature measured should include this self-temperature rise. Therefore, it is required to limit capacitor surface temperature including self -generated heat should not exceed the maximum operating temperature of +85°C.</li> <li>Operating Environment precautions</li> <li>1. Capacitors should not be used in the following environments: (1)Environmental conditions to avoid         <ul> <li>a. exposure to water or salt water.</li> <li>b. exposure to moisture or condensation.</li> <li>c. exposure to corrosive gases (such as hydrogen sulfide, sulfurous acid, chlorine, and ammonia)</li> </ul> </li> </ul>
Technical considerations	<ul> <li>1-1. When an AC or a pulse voltage is applied to capacitors specified for DC use, even if the voltage is less than the rated voltage, the AC current or pulse current running through the capacitor will cause the capacitor to self-generate heat because of the loss characteristics.         The amount of heat generated depends on the dielectric materials used, capacitance, applied voltage, frequency, voltage waveform, etc. The surface temperature changes due to emitted heat which differs by capacitor shape or mounting method.     </li> <li>Please contact Taiyo Yuden with any questions regarding emitted heat levels in your particular application. It is recommended the temperature rise be measured in the actual circuit to be used.     </li> <li>1-2. For capacitors, the voltage and frequency relationship is generally determined by peak voltage at low frequencies, and by self-generated heat high frequencies. (Refer to the following curve.)         Sum of the peak voltage         (peak to peak)         Sum of the peak voltage         (peak to peak)         Difference in self-generated heat limit         Frequency         Frequency         Frequency         Frequency         Output         Frequency         Event of the capacitance of the provide the capacitance of the capacita</li></ul>

2. PCB Design	
Precautions	<ul> <li>Design of the capacitor mount</li> <li>1. When capacitors are mounted onto a PC board, hole dimensions on the board should match the lead pitch of the component, if not it will cause breakage of the terminals or cracking of terminal roots covered with resin as excess stress travels through the terminal legs. As a result, humidity resistance performance would be lost and may lead to a reduction in insulation resistance and cause a withstand voltage failure.</li> </ul>

3. Considerations	3. Considerations for automatic insertion		
Precautions	<ul> <li>Adjustment Automatic Insertion machines (leaded components)</li> <li>Precautions</li> <li>1. When inserting capacitors in a PC board by auto-insertion machines the impact load imposed on the capacitors should be minimized t prevent the leads from chucking or clinching.</li> </ul>		
Technical considerations	<ol> <li>When installing products, care should be taken not to apply distortion stress as it may deform the products.</li> <li>Our company recommends the method to place the lead with fewer loads that join the product.</li> </ol>		

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	◆Selection of Flux
	1. When soldering capacitors are on the board, flux should be applied thinly and evenly.
	2. Flux used should be with less than or equal to 0.1 wt% (equivalent to Chlorine) of halogenated content. Flux having a strong acidity
	content should not be applied.
	3. When using water-soluble flux, special care should be taken to properly clean the boards.
	♦Wave Soldering
Precautions	1. Temperature, time, amount of solder, etc. are specified in accordance with the following recommended conditions.
1 1 ooddallonio	2. Do not immerse the entire capacitor in the flux during the soldering operation. Only solder the lead wires on the bottom of the board.
	◆Recommended conditions for using a soldering iron:
	1. Put the soldering iron on the land-pattern.
	Soldering iron's temperature – below 350°C
	Duration – 3 seconds or less
	Numbers of times – 1 times
	The soldering iron should not directly touch the capacitor.
	♦ Selection of Flux
	1. Flux is used to increase solderability in wave soldering, but if too much is applied, a large amount of flux gas may be emitted and may
	detrimentally affect solderability. To minimize the amount of flux applied, it is recommended to use a flux-bubbling system.
	2. With too much halogenated substance (Chlorine, etc.) content is used to activate the flux, an excessive amount of residue after soldering
	may lead to corrosion of the terminal electrodes or degradation of insulation resistance on the surface of the capacitors.
	3. Since the residue of water-soluble flux is easily dissolved by water content in the air, the residue on the surface of capacitors in high
	humidity conditions may cause a degradation of insulation resistance and therefore affect the reliability of the components. The
Technical	cleaning methods and the capability of the machines used should also be considered carefully when selecting water-soluble flux.
considerations	◆Wave Soldering
Considerations	1. If capacitors are used beyond the range of the recommended conditions, heat stresses may cause cracks inside the capacitors, and
	consequently degrade the reliability of the capacitors.
	2. When the capacitors are dipped in solder, some soldered parts of the capacitor may melt due to solder heat and cause short-circuits or
	cracking of the ceramic material. Deterioration of the resin coating may lower insulation resistance and cause a reduction of withstand
	voltage.
	♦Recommended conditions for using a soldering iron:
	1. If products are used beyond the range of the recommended conditions, heat stress may deform the products, and consequently degrade
	the reliability of the products.

5. Cleaning	
Precautions	<ul> <li>Board cleaning</li> <li>1. When cleaning the mounted PC boards, make sure that cleaning conditions are consistent with prescribed usage conditions.</li> </ul>
Technical considerations	<ol> <li>The resin material used for the outer coating of capacitors is occasionally a wax substance for moisture resistance which can easily be dissolved by some solutions.</li> <li>So before cleaning, special care should be taken to test the component's vulnerability to the solutions used.</li> <li>When using water-soluble flux please clean the PCB with purified water sufficiently and dry thoroughly at the end of the process. Insufficient washing or drying could lower the reliability of the capacitors.</li> </ol>

6. Post-cleaning	-process
Precautions	<ul> <li>Application of resin molding, etc. to the PCB and components.</li> <li>Please contact your local Taiyo Yuden sales office before performing resin coating or molding on mounted capacitors. Please contact your local Taiyo Yuden sales office in case of sealing the capacitor with resin or molding it on mounted capacitors. Please verify that the sealing or molding does not affect on the actual application in quality.</li> </ul>
Technical considerations	<ul> <li>1-1. The thermal expansion and coefficient of contraction of the molded resin are not necessarily matched with those of the capacitor. The capacitors may be exposed to stresses due to thermal expansion and contraction during and after hardening. This may lower the specified characteristics and insulation resistance or cause reduced withstanding voltage by cracking the ceramic or separating the coated resin from the ceramics.</li> <li>1-2. With some types of mold resins, the resin's decomposition gas or reaction gas may remain inside the resin during the hardening period or while left under normal conditions, cause a deterioration of the capacitor's performance.</li> <li>1-3. Some mold resins may have poor moisture proofing properties. Please verify the contents of the resins before they are applied.</li> </ul>
	1-4. Please contact Taiyo Yuden before using if the hardening process temperature of the mold resins is higher than the operating temperature of the capacitors.

7. Handling	
Precautions	<ul> <li>Mechanical considerations</li> <li>1. Be careful not to subject the capacitors to excessive mechanical shocks. Withstanding voltage failure may result.</li> <li>2. If ceramic capacitors are dropped onto the floor or a hard surface they should not be used.</li> </ul>
Technical considerations	<ol> <li>Because the capacitor is made of ceramic, mechanical shocks applied to the board may damage or crack the capacitors.</li> <li>Ceramic capacitors which are dropped onto the floor or a hard surface may develop defects and have a higher risk of failure over time.</li> </ol>

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8. Storage conditions
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Precautions	<ul> <li>Storage</li> <li>1. To maintain the solderability of terminal electrodes and to keep the packaging material in good condition, care must be taken to control temperature and humidity in the storage area. Humidity should especially be kept as low as possible. Recommended conditions: Ambient temperature Below 40 °C Humidity Below 70% RH.</li> <li>Products should be used within 6 months after delivery. After the above period, the solderability should be checked before using the capacitors.</li> <li>2. Capacitors should not be kept in an environment filled with decomposition gases such as sulfurous hydrogen, sulfurous acid, chlorine, ammonia. etc.</li> </ul>
	3. Capacitors should not be kept in a location where they may be exposed to moisture, condensation or direct sunlight.
Technical considerations	1. Under high temperature/high humidity conditions, the decrease in solderability due to the oxidation of terminal electrodes and deterioration of taping and packaging characteristics may be accelerated.

